

Absolute Maximum Ratings

PWR to PGND	-0.3V to +18V
PVIN to PGND	-0.3V to +18V
LX to PGND	-0.3V to ($V_{PVIN} + 0.3V$)
LXSNS to SGND	-2V to +14V
INSNS to SGND	-0.3V to +14V
OUTP, OUTN, DCRP, DCRN to SGND	-0.3V to +5.5V
3P3 to SGND	-0.3V to the minimum of +4V or ($V_{GDRV} + 0.3V$)
GDRV to SGND	-0.3V to the minimum of +6V or ($V_{PWR} + 0.3V$)
LBI to PGND	-0.3V to ($V_{PWR} + 0.3V$)
LBO to PGND	($V_{GDRV} - 0.3V$) to ($V_{GDRV} + 0.3V$)
BST to LX	-0.3V to +6V
BST to PGND	-0.3V to +24V
BST to GDRV	-0.3V to +24V

1P8 to DGND	-0.3V to +2.2V
CIO, SET, PG, ADDR0, ADDR1, SYNC, TEMPX, SALRT to DGND	-0.3V to +4V
EN, SCL, SDA to DGND	-0.3V to +4V
PGND to SGND	-0.3V to +0.3V
DGND to SGND	-0.3V to +0.3V
Electrostatic Discharge (ESD) Rating	
Human Body Model (HBM)	±2500V
Junction Temperature	+125°C
Operating Temperature Range	-40°C to +85°C
Continuous Power Dissipation ($T_A = +70^\circ\text{C}$)	
TQFN (derate 37mW/°C above +70°C)	2963mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C
Soldering Temperature (reflow)	+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Thermal Characteristics (Note 1)

TQFN

Junction-to-Ambient Thermal Resistance (θ_{JA})27°C/W

Junction-to-Case Thermal Resistance (θ_{JC}).....1.7°C/W

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

Electrical Characteristics

(All settings = factory default, $V_{PWR} = V_{PVIN} = V_{INSNS} = 12V$, $V_{SGND} = V_{DGND} = V_{PGND} = 0V$, $V_{OUT} = 1.2V$, $f_{SW} = 600kHz$. Specifications are for $T_A = T_J = -40^\circ\text{C}$ to $+85^\circ\text{C}$, typical values are at $T_A = T_J = +25^\circ\text{C}$. See the [Typical Operating Circuit](#), unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
INPUT SUPPLY						
Input Voltage Range	V _{PWR}		4.5		14	V
Input Supply Current	I _{PWR}	BabyBuck bias supply, driver not switching	10			mA
		Linear mode bias supply, driver not switching	2450			
Input Overvoltage-Lockout Threshold	V _{OVLO(PWR)}	Input rising	14.3	15.2	16.0	V
Input Undervoltage-Lockout Threshold	V _{UVLO(PWR)}	Rising edge	3.8	4.1	4.4	V
		Hysteresis	0.24			
BIAS REGULATORS						
3P3 Output Voltage	V _{3P3}	I _{LOAD(3P3)} = 0mA	3.3			V
1P8 Output Voltage	V _{1P8}	I _{LOAD(1P8)} = 0mA	1.80			V
STARTUP/SHUTDOWN TIMING						
Firmware Initialization	t ₁	From V _{IN} > V _{UVLO(PWR)} , until ready to enable (Figure 2)	25			ms

Electrical Characteristics (continued)

(All settings = factory default, $V_{PWR} = V_{PVIN} = V_{INSNS} = 12V$, $V_{SGND} = V_{DGND} = V_{PGND} = 0V$, $V_{OUT} = 1.2V$, $f_{SW} = 600kHz$. Specifications are for $T_A = T_J = -40^{\circ}C$ to $+85^{\circ}C$, typical values are at $T_A = T_J = +25^{\circ}C$. See the [Typical Operating Circuit](#), unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Minimum Programmable t_{ON_DELAY}	t_2	(Figure 2, Note 10)	1			ms
Minimum Programmable Turn-On Rise Time	t_3	(Figure 2, Note 10)	1			ms
Adaptive Tuning Time	t_4	From $V_{OUT} = V_{OUT}$ command to assertion of power good (PG) (Figure 2)		12		ms
OUTPUT VOLTAGE						
Programmable Output Voltage Range	V_{OUT}	Measured from OUTP to OUTN (Notes 4 and 10)	0.5		5.25	V
LX Bias Current	I_{LX}	Not switching, current out of device pin		200		μA
Allowable Duty-Cycle Range		(Note 10)	5		95	%
Regulation Set-Point Accuracy (Note 3)		$V_{OUT} > 0.8V, -40^{\circ}C \leq T_A \leq +85^{\circ}C$	-1.26		+1.26	%
		$V_{OUT} \leq 0.8V, -40^{\circ}C \leq T_A \leq +85^{\circ}C$	-1.95		+1.95	
V_{OUT} Sense Bias Current	I_{OUTP}	Current flowing into OUTP		50		μA
	I_{OUTN}	Current flowing out of OUTN		35		μA
DCR Sense Bias Current	I_{DCRP}	Current flowing into DCR, $V_{DCRP} - V_{DCRN} = 150mV$		120		nA
	I_{DCRN}			4		μA
PWM CLOCK (Note 3)						
Switching-Frequency Range	f_{SW}	Note 10	300		1000	kHz
Switching-Frequency Set-Point Accuracy			-5		+5	%
External Clock to SYNC Frequency Range	f_{SYNC}		300		1000	kHz
Minimum Allowable SYNC Duty Cycle				40		%
Maximum Allowable SYNC Duty Cycle				60		%
PROTECTION (Note 3)						
Overcurrent Fault-Threshold Accuracy		$T_A = +25^{\circ}C$, exclusive of sensor error		± 3		%
Output Overvoltage-Fault Threshold		Output rising		115		% V_{OUT}
Output Undervoltage-Fault Threshold		Output falling		85		% V_{OUT}
Thermal-Shutdown Threshold Accuracy				± 20		$^{\circ}C$
Thermal-Shutdown Hysteresis				20		$^{\circ}C$
Power-Good Threshold		V_{OUT} rising		90		% V_{OUT}
		V_{OUT} falling		85		

Electrical Characteristics (continued)

(All settings = factory default, $V_{PWR} = V_{PVIN} = V_{INSNS} = 12V$, $V_{SGND} = V_{DGND} = V_{PGND} = 0V$, $V_{OUT} = 1.2V$, $f_{SW} = 600kHz$. Specifications are for $T_A = T_J = -40^{\circ}C$ to $+85^{\circ}C$, typical values are at $T_A = T_J = +25^{\circ}C$. See the [Typical Operating Circuit](#), unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
STARTUP/SHUTDOWN TIMING						
Firmware Initialization	t ₁	From V _{IN} > V _{UVLO(PWR)} , until ready to enable (Figure 2)		25		ms
Programmable TON_DELAY, TOFF_DELAY Range	t ₂	Minimum delay (Figure 2)		1		ms
		Maximum delay (Figure 2)		145		
TON_DELAY, TOFF_DELAY Resolution		Delay timing step size		0.6		ms
TON_DELAY, TOFF_DELAY Command Accuracy (Note 10)		Command value sent vs. read back			±0.3	ms
TON_DELAY, TOFF_DELAY Timing Accuracy		Command read-back value vs. actual delay time		±0.8		ms
Programmable TON_RISE, TOFF_FALL Range	t ₃	Minimum (Figure 2)		1		ms
		Maximum (Figure 2)		255 x t _{RR}		
TON_RISE, TOFF_FALL Resolution	t _{RR}	Ramp timing step size (varies with VOUT_COMMAND)		0.4 - 1.0		ms
TON_RISE, TOFF_FALL Command Accuracy (Note 10)		Command value sent vs. read back			±0.5	ms
TON_RISE, TOFF_FALL Timing Accuracy		Command read back value vs. actual ramp duration		±10		µs
Adaptive Tuning Time	t ₄	From end of soft-start ramp to PG assertion (varies with FREQUENCY_SWITCH (Figure 2)		12		ms
Temperature-Measurement Accuracy		External		±5		°C
		Internal		±5		
DIGITAL I/O						
Power-Good Logic-High Leakage Current		Open-drain output mode, open-drain connected to 5.5V, V _{3P3} = 3.3V			10	µA
Output Logic-High		CMOS mode, I _{SOURCE} = 4mA	V _{3P3} - 0.4		V _{3P3}	V
Output Logic-Low		I _{SINK} = 4mA			0.4	V
Input Bias Current			-1		+1	µA
Rise/Fall Slew Rate		C _{LOAD} = 15pF		2		ns
EN, SYNC Input-Logic Low Voltage		Input voltage falling			0.8	V
EN, SYNC Input-Logic High Voltage		Input voltage rising	2			V

Electrical Characteristics (continued)

(All settings = factory default, $V_{PWR} = V_{PVIN} = V_{INSNS} = 12V$, $V_{SGND} = V_{DGND} = V_{PGND} = 0V$, $V_{OUT} = 1.2V$, $f_{SW} = 600kHz$. Specifications are for $T_A = T_J = -40^{\circ}C$ to $+85^{\circ}C$, typical values are at $T_A = T_J = +25^{\circ}C$. See the [Typical Operating Circuit](#), unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
EN, SYNC Input Leakage Current			-10		+10	μA
SMBus (Note 3)						
SDA, SCL Input Logic-Low Voltage		Input voltage falling			0.8	V
SDA, SCL Input Logic-High Voltage		Input voltage rising	2			V
SDA, SCL, \overline{SALRT} Logic-High Leakage Current		V_{SCL} , $V_{SDA} = 0V$, and $V_{\overline{SALRT}}$ tested at 0V and 3.3V			10	μA
SDA, SCL, \overline{SALRT} Logic-Low Output Voltage		$I_{SINK} = 4mA$			0.4	V
PMBus Operating Frequency	f_{SMB}			400		kHz
Bus Free Time (STOP - START)	t_{BUF}		1.3			μs
START Condition Hold Time from SCL	$t_{HD:STA}$		0.6			μs
START Condition Setup Time from SCL	$t_{SU:STA}$		0.6			μs
STOP Condition Setup Time from SCL	$t_{SU:STO}$		0.6			μs
SDA Hold Time from SCL	$t_{HD:DAT}$		300			ns
SDA Setup Time from SCL	$t_{SU:DAT}$		100			ns
SCL Low Period	t_{LOW}		1.3			μs
SCL High Period	t_{HIGH}		0.6			μs
THERMAL PROTECTION						
Gate-Driver Thermal-Shutdown Threshold	T_{SHDN}	Hysteresis = $+20^{\circ}C$		150		$^{\circ}C$
INTEGRATED SWITCHING MOSFETS						
High-Side nMOS On-Resistance	R_{ONH}			40	60	$m\Omega$
Low-Side nMOS On-Resistance	R_{ONL}			20	30	$m\Omega$
Maximum Allowable High-Side nMOS Average Current		$V_{OUT} = 1.8V$			4.3	A
Maximum Allowable Low-Side nMOS Average Current		$V_{OUT} = 1.8V$			6.0	A
V_{GDRV} Undervoltage Lockout		GDRV falling	3.6	3.85	4.1	V
		GDRV rising	3.7	3.94	4.2	
V_{GDRV} Output	V_{GDRV}	$I_{LOAD} = 1mA$ to $100mA$, $V_{IN} = 6V$ to $14V$	4.5	5.0	5.5	V

Electrical Characteristics (continued)

(All settings = factory default, $V_{PWR} = V_{PVIN} = V_{INSNS} = 12V$, $V_{SGND} = V_{DGND} = V_{PGND} = 0V$, $V_{OUT} = 1.2V$, $f_{SW} = 600kHz$. Specifications are for $T_A = T_J = -40^{\circ}C$ to $+85^{\circ}C$, typical values are at $T_A = T_J = +25^{\circ}C$. See the [Typical Operating Circuit](#), unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
BabyBuck REGULATOR						
BabyBuck Oscillator Frequency			1	2	3.4	MHz
nMOS On-Resistance				4.5	9.5	Ω
nMOS On-Resistance				2.0	4.0	Ω
Current-Sense Resistance	R_{CSP}	LBI to GDRV resistor	0.65	1.1	1.6	Ω
Current Limit	I_{LIM}			491	900	mA
Dropout Voltage	V_{DO}	$I_{LOAD} = 100mA$, $V_{IN} = 4.9V$		256		mV
Foldback Current Limit	I_{LIMFB}	$V_{GDRV} = 0V$		20		mA
Full Current Limit	I_{LIMF}	$V_{GDRV} = 4V$		182		mA
BOOTSTRAP CIRCUIT						
BST Charging Switch $R_{DS(ON)}$		$V_{GDRV} = 5V$, $LX = 0V$ (pulldown state), $I_{BST} = 100mA$		1.61		Ω
BST to LX Supply Current		$V_{GDRV} = 0V$, $LX = 0V$ (pulldown state), $V_{BST} = 5V$		250		μA

Note 2: Limits are 100% production tested at $T_A = +25^{\circ}C$. Maximum and minimum limits over temperature are guaranteed through correlation using statistical quality control (SQC) methods. Typical values are expressed as factory-default values also for configurable specifications within a range.

Note 3: Design guaranteed by bench characterization. Limits are not production tested.

Note 4: The settable output voltage range is 0.6V to 5.0V. This range expands to 0.5V to 5.25V when the voltage-margining function is enabled.

Note 5: Can go to 0% or 100% during a transient.

Note 6: Once the device locks onto an external synchronizing clock, the tolerance on the capture range is $\pm 10\%$.

Note 7: See the [Voltage Tracking](#) section.

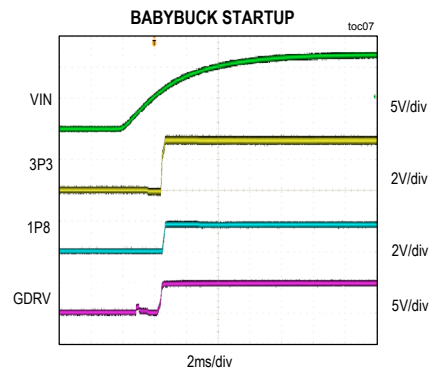
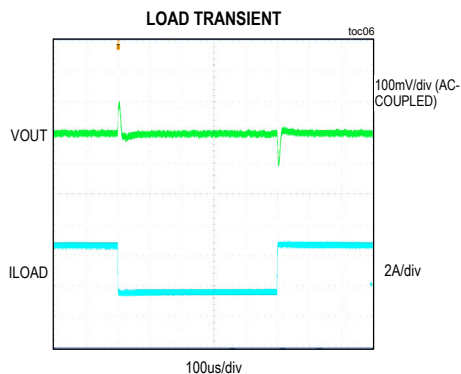
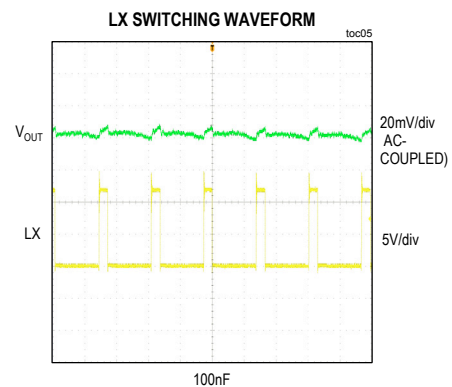
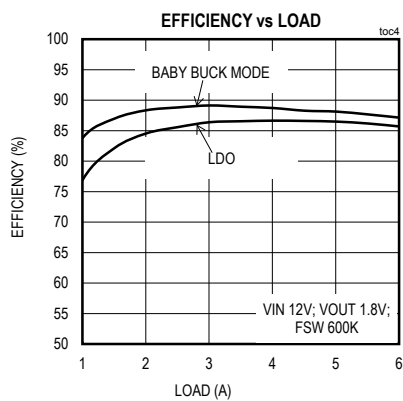
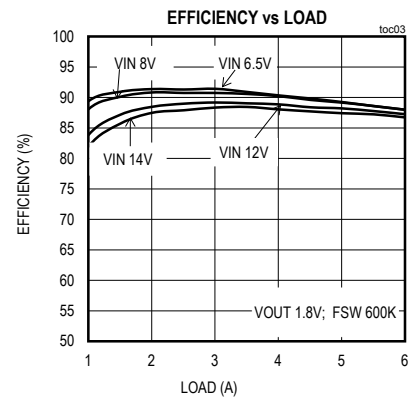
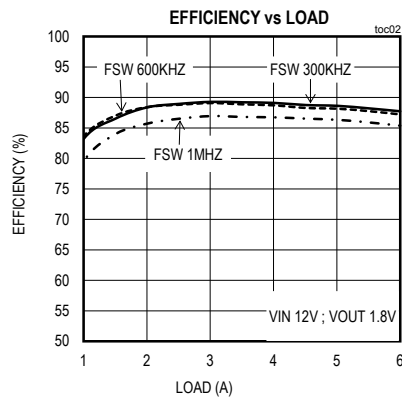
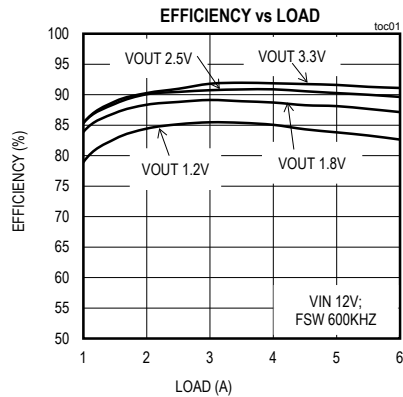
Note 8: Excluding tracking mode.

Note 9: Voltage-regulation accuracy is power-stage dependent; adherence to all data sheet design recommendations is required to achieve specified accuracy.

Note 10: Customer-programmable parameters.

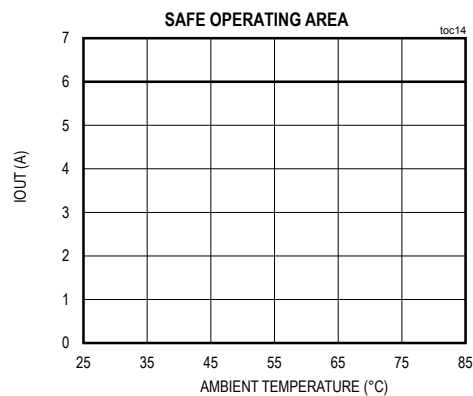
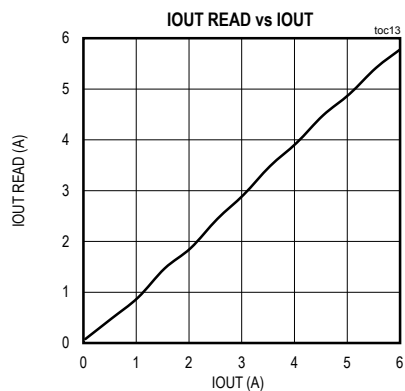
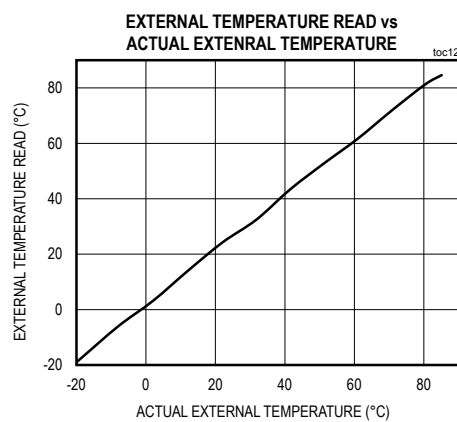
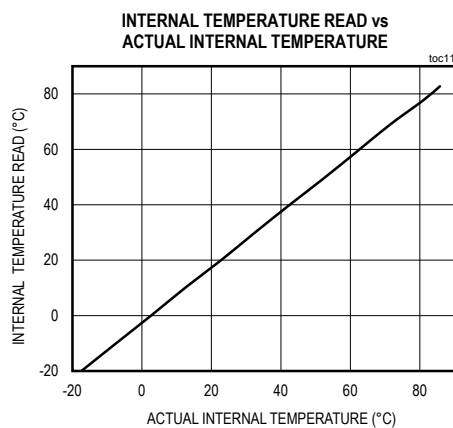
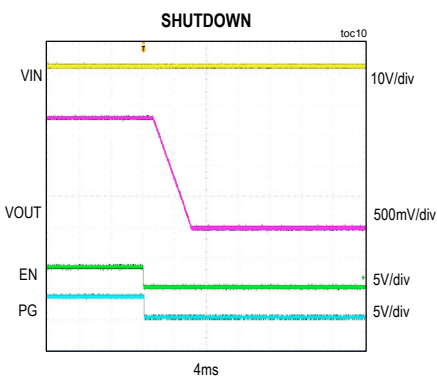
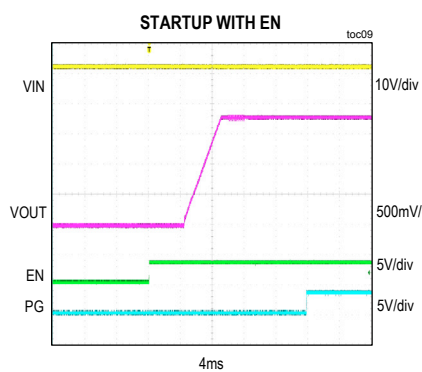
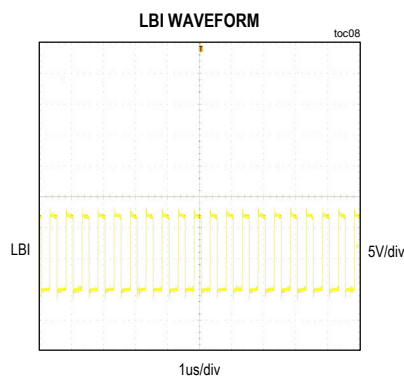
Typical Operating Characteristics

($T_A = +25^\circ\text{C}$, $V_{IN} = 12\text{V}$, $V_{OUT} = 1.2\text{V}$, $f_{SW} = 600\text{kHz}$, unless otherwise noted. See the *Typical Operating Circuit* and Application 1 in Table 8).



Typical Operating Characteristics (continued)

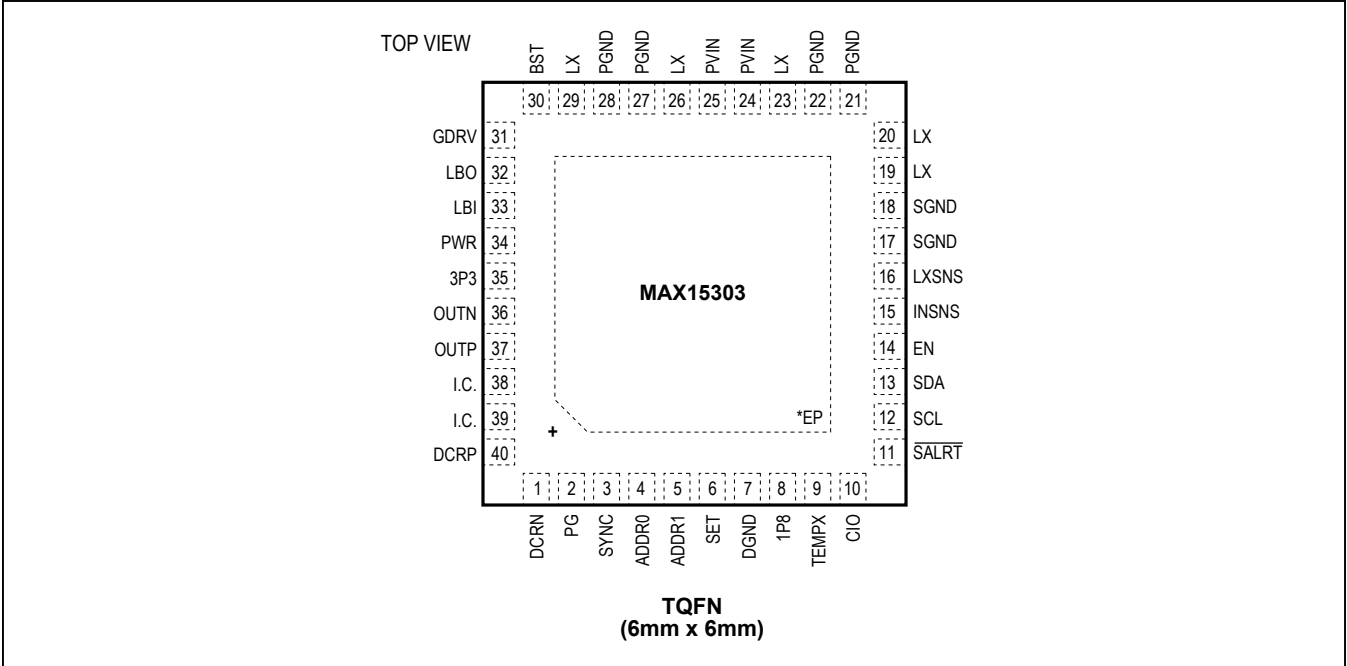
($T_A = +25^\circ\text{C}$, $V_{IN} = 12\text{V}$, $V_{OUT} = 1.2\text{V}$, $f_{SW} = 600\text{kHz}$, unless otherwise noted. See the *Typical Operating Circuit* and Application 1 in Table 8).



MAX15303

6A Digital PoL DC-DC Converter with
InTune Automatic Compensation

Pin Configuration



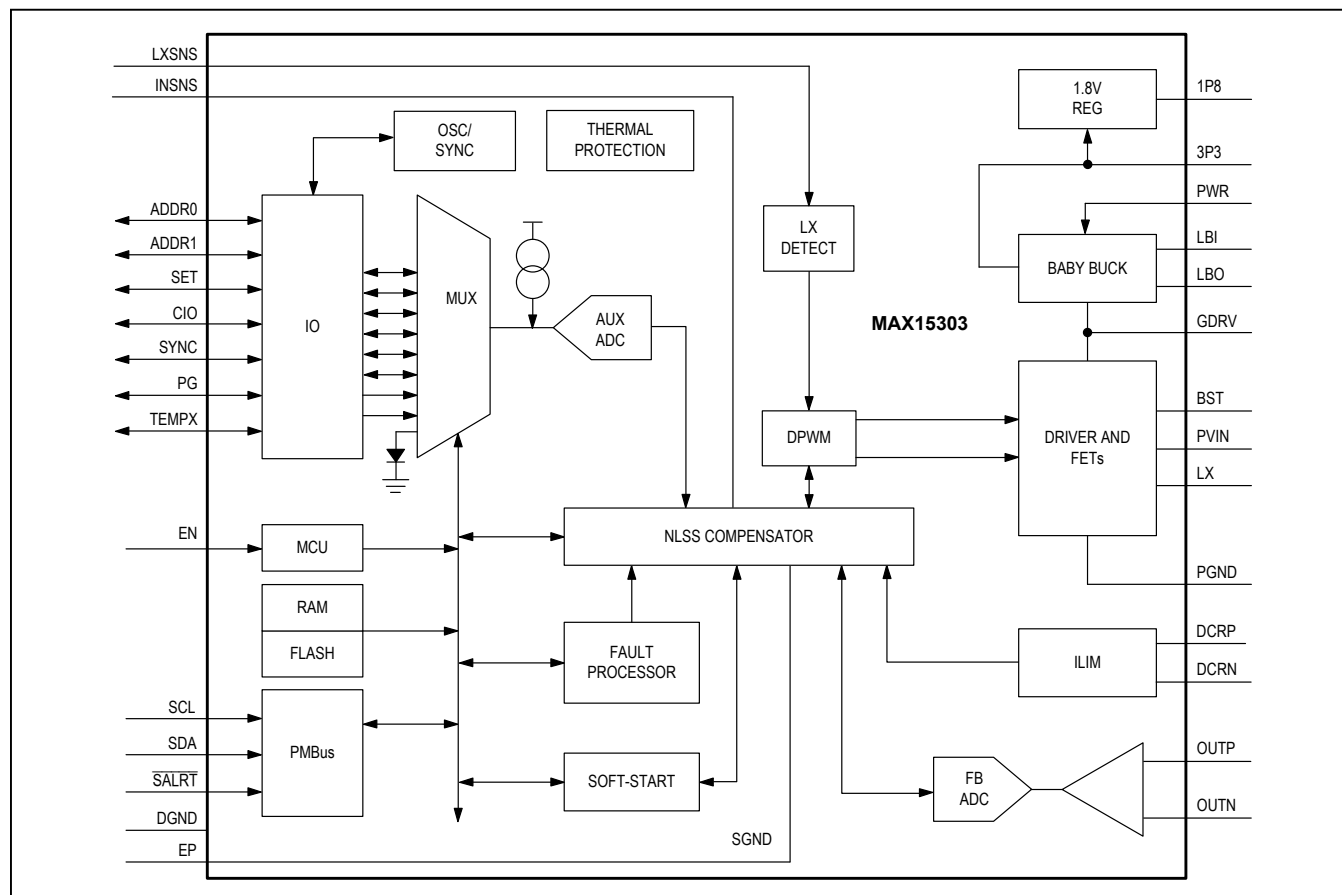
Pin Description

PIN	NAME	FUNCTION
1	DCRN	Output Current Differential-Sense Negative Input. Connect to the inductor or current-sense element negative side.
2	PG	Open-Drain Power-Good Indicator. PG asserts high when soft-start is complete, the voltage has reached regulation, and after a successful InTune calibration is completed.
3	SYNC	External Switching-Frequency Synchronization Input. Connect a resistor between SYNC and SGND to set the switching frequency of the DC-DC converter (see Table 3). The device can also synchronize with an external clock applied at SYNC.
4	ADDR0	SMBus Address-Select Input 0. Used with ADDR1 to assign a unique SMBus address to the device.
5	ADDR1	SMBus Address-Select Input 1. Used with ADDR0 to assign a unique SMBus address to the device and set the current limit for the device.
6	SET	Output-Voltage Set Input. Connect a resistor between SET and SGND to set the output voltage. Shorting this pin to ground selects tracking mode (see Table 1).
7	DGND	Digital Ground. Connect to the exposed pad (EP).
8	1P8	Internal 1.8V Regulator Output. 1P8 is the supply rail for the internal digital circuitry. Bypass 1P8 pin to DGND with a 10µF ceramic capacitor. This pin cannot be used to power any circuitry external to the device.
9	TEMPX	Connection for the External Temperature Sensor. Connect an npn transistor junction from TEMPX to SGND to measure the temperature at any point on the PCB. Place a 100pF ceramic capacitor in parallel with the temperature-sense junction.
10	CIO	Configurable Input/Output Pin. This is a voltage-tracking input when SET is connected to SGND to select tracking mode. CIO must be grounded when not in tracking mode.

Pin Description (continued)

PIN	NAME	FUNCTION
11	$\overline{\text{SALRT}}$	SMBus Alert. Interrupt to the SMBus master. Open-drain output that pulls low when SMBus interaction is required.
12	SCL	SMBus Clock Input
13	SDA	SMBus Data Input/Output
14	EN	Enable Input. Do not leave unconnected. By default, driving EN high enables output regulation, and driving EN low disables output regulation.
15	INSNS	Power-Train Input Rail Sense. Monitors the input supply of the DC-DC converter. Connect a series 2k Ω resistor between input rail and INSNS pin.
16	LXSNS	Switching-Node Sense Input. Connect a series 2k Ω resistor between the switching node and the LXSNS pin.
17, 18	SGND	Analog Ground. Connect to the exposed pad (EP).
19, 20, 23, 26, 29	LX	Switching Node. Connect directly to the high side of the output inductor. Connect a Schottky diode between LX and PGND.
21, 22, 27, 28	PGND	Power Ground. Connect to SGND and DGND using short wide PCB traces.
24, 25	PVIN	Power-Supply Input for the Power Stage. Connect to a 4.5V to 14V supply. Must be connected to the same voltage as PWR.
30	BST	Bootstrap Capacitor Connection. Connect a 0.22 μ F ceramic capacitor between BST and the switching node.
31	GDRV	Gate-Driver Supply. Bypass GDRV to PGND with a 2.2 μ F ceramic capacitor.
32	LBO	BabyBuck Switching-Node 2. See the <i>BabyBuck Gate-Driver Regulator</i> section for configurations.
33	LBI	BabyBuck Switching-Node 1. See the <i>BabyBuck Gate-Driver Regulator</i> section for configurations.
34	PWR	Power Supply Input for the Bias Circuitry. Connect to a 4.5V to 14V supply. Must be connected to the same voltage as PVIN.
35	3P3	Internal 3.3V Regulator Output. 3P3 is the supply rail for the internal analog circuitry. Bypass 3P3 to SGND with a 4.7 μ F ceramic capacitor. This pin cannot be used to power any circuitry external to the device.
36	OUTN	Output-Voltage Differential-Sense Negative Input. Connect to ground at the load.
37	OUTP	Output-Voltage Differential-Sense Positive Input. Connect to the output voltage at the load.
38, 39	I.C.	Internally Connected. Connect these pins to the exposed pad (EP).
40	DCRP	Output-Current Differential-Sense Positive Input. Connect to the inductor or current-sense element positive side.
—	EP (SGND)	Exposed Pad and Analog Ground. The EP serves two purposes: it is both the analog ground of the device and a conduit for heat transfer. Connect to large ground plane to maximize thermal performance. See the <i>PCB Layout Guidelines</i> section.

Functional Diagram



Detailed Description

The MAX15303 is an innovative, PMBus-compliant, mixed-signal power-management IC with a built-in high-performance digital PWM controller for POL applications. The device is based on Maxim's InTune automatically compensated digital PWM control loop. The device has optimal partitioning of the digital power management and the digital power-conversion domains to minimize startup times and reduce bias current. The device supports over 80 standard and manufacturer-specific PMBus commands.

The device uses adaptive compensation techniques to handle a broad range of timing, voltage, current, temperature, and external component parameter variations. Efficiency-optimization techniques further enhance the performance of the device, including internal MOSFETs, with internally optimized gate drive, and the switch-mode BabyBuck bias regulators for biasing the internal circuit blocks and the MOSFET gate drive.

The device's BabyBuck is an integrated power converter used to self-bias the digital, analog, and driver blocks from a single input supply (V_{PWR}). The device relies on mixed-signal design techniques to control the power system efficiently and precisely. It does not require any software to configure or initialize the device. In addition, many operating features can be monitored and configured through the SMBus interface using standard PMBus commands, resulting in ease of design and flexibility.

The control loop is separated from the housekeeping, power-monitoring, and fault-management blocks. Control-loop parameters are stored in an on-chip nonvolatile flash memory. An internal microcontroller enables monitoring operating conditions using the SMBus interface. The digital pulse-width modulator (DPWM) control loop is implemented using dedicated state machines, so there is no DSP or MCU in the control loop. This partition allows the chip architecture to minimize power consumption while optimizing performance.

The *Functional Diagram* shows the controller implementation using a digital state-space compensator (model predictive) controller, a microcontroller unit (MCU), a DPWM, a PLL-based master timing generator, and a PMBus serial communication port.

State-Space Controller and DPWM

The device uses a digital DPWM control scheme to regulate the output voltage. Traditional PWM regulators (both analog and digital) use classical control methods for DC-DC converters, based on linear models of a discrete time nature and root locus, Bode and Nyquist plots. These linear time-invariant approximations work well for small signals. However, when large transients cause duty-cycle saturation, the performance of the closed loop can be degraded (larger overshoots) and the output transients are “slower” (large settling times). Tighter regulation performance during these disturbances is becoming a requirement. The device addresses the issue by using model-predictive-based feedback design to compensate the DPWM.

The device automatically constructs a state-space model (state estimator) of the control plant (*Figure 1*). The internal model gives access to state-control variables that are otherwise unavailable. The state-control variables are used to set the proper control values. For a given input-to-output step-down ratio and PWM switching frequency, the device sets the compensation coefficients for that application. Upon output enable, or in response to a

PMBus command, the device performs the InTune calibration. During this calibration several power-train parameter values are measured and the extracted parameters are used to create the internal model to optimize the bandwidth and transient response of the converter.

The state-space compensator block generates the duty-cycle command for the DPWM block. The DPWM block generates the required PWM outputs for the driver.

BabyBuck Gate-Driver Regulator

The device contains an internal bias supply that generates both the gate-drive voltage supply and the internal digital supply to power the controller. This BabyBuck gives the user two options to allow optimal configuration the device for their specific system requirements, BabyBuck mode and LDO mode.

In BabyBuck mode, the internal regulator is configured as a two-output switching regulator that uses a small (1008 size), low-cost inductor. The switching supply efficiently converts the higher input voltage to the lower bias supply and gate-drive voltages. BabyBuck mode is typically used with higher input voltages ($> 7V$) to improve overall system efficiency. BabyBuck mode cannot be used with input voltages lower than 6.5V. To configure the device in BabyBuck mode, connect PWR to the input voltage (PVIN) and connect the recommended inductor between LBI and LBO.

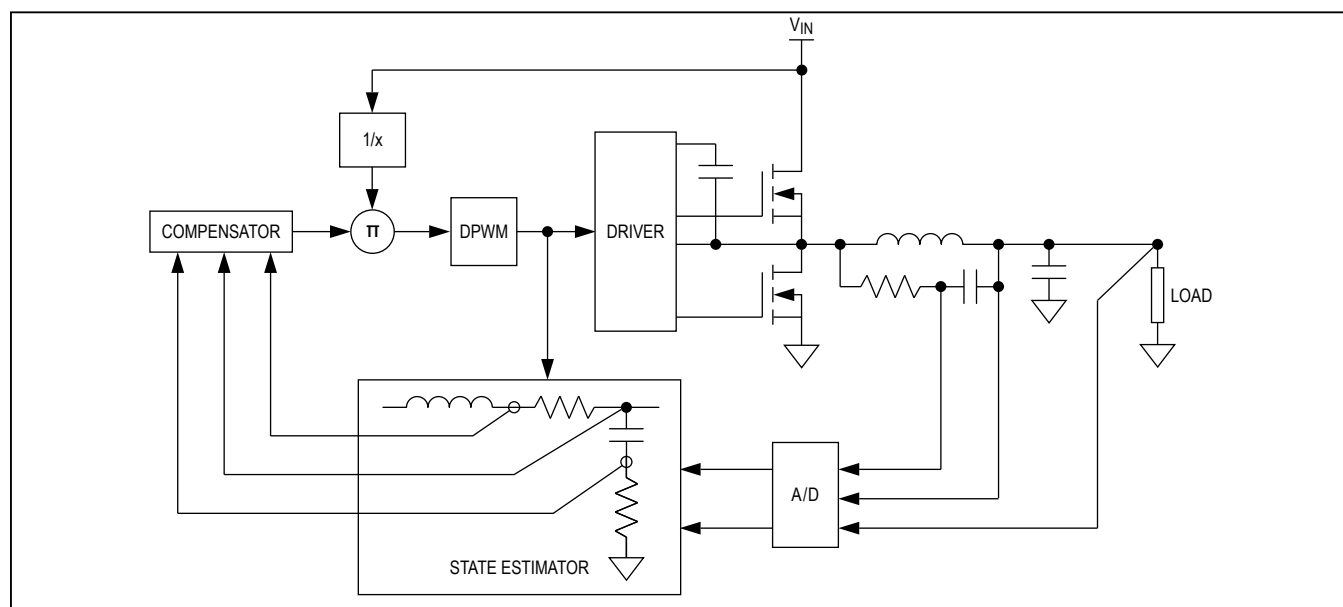


Figure 1. State-Space Controller Concept

In LDO mode, the device reconfigures BabyBuck to linearly regulate the input voltage down to the gate drive and bias voltages. LDO mode is typically used with lower input voltages (5V to 9V) or when the user wants to eliminate the BabyBuck inductor; however, it can also be used at higher input voltages as well. To configure the device in LDO mode, connect PWR to the input voltage (PVIN) and connect a 100kΩ resistor between PWR and LBI. Leave LBO unconnected.

Temperature Sense

The device provides both an internal and external temperature measurement. Both the internal and external temperatures are reported to the user through the PMBus commands `READ_TEMPERATURE_1` and `READ_TEMPERATURE_2`, respectively. The internal temperature is measured directly at the device silicon junction. The external temperature is measured through the TEMPX pin using the base-emitter junction of a standard 2N3904 transistor. This technique is widely employed because it requires no calibration of the sensor. Any PN junction can be used as a temperature sensor. The 2N3904, 2N2222 transistors and integrated thermal diodes found in microprocessors, FPGAs, and ASICs are commonly used temperature sensors. Connect a 100pF filter capacitor, as shown in [Figure 7](#), to ensure accurate temperature measurements.

When the 2N3904 is connected to the TEMPX pin, the device uses the external temperature information for temperature-fault and current-measurement temperature compensation (tempco). If the external temperature measurement is not used or measures out of range, the device uses the internal temperature for temperature compensation and thermal-fault protection. Disable the external temperature measurement by connecting TEMPX to ground.

The device temperature fault thresholds are programmed through the PMBus interface. The default value for the thermal-shutdown threshold is +115°C. The default overtemperature response is to shut down and restart when the fault is no longer present. Note that a rising temperature faults when it crosses the `OT_FAULT_LIMIT` and clears when it falls below the `OT_WARN_LIMIT`. The `OT_WARN_LIMIT` should always be set below the `OT_FAULT_LIMIT`. The device shuts down and pulls PG low when it acts on a temperature fault.

Regulation and Monitoring Functions

The device improves the reliability of the system it powers with multiple circuits that protect the regulator and the load from unexpected system faults. The device continuously monitors the input voltage, output voltage and current, and internal/external temperatures. The device can be configured to provide alerts for specific conditions of the monitored parameters. The thresholds and responses for these parameters have factory-default values, but can also be configured through the PMBus interface. The status of the power supply can be queried any time by a PMBus master.

Regulator Parameters

Key operating parameters in the device, such as output voltage, switching frequency, and current-sense resistance, can be configured using resistors. This provides flexibility for the user while ensuring that the device has a well-defined “out-of-the-box” operational state. The pin configurations are only sampled when power is first applied (the device ignores changes to resistor settings after power-up). From this initial operating state, the user can change the parameters using PMBus commands. These changes can be stored in nonvolatile memory, allowing the device to subsequently power up into the customers specifically stored configuration state. However, it is recommended that the pin-strap or resistor settings always be applied with values chosen to provide a safe initial behavior prior to PMBus configuration.

Pin-strap settings are programmed by connecting a resistor from the appropriate device pins to SGND. The device reads the resistance at startup and sets command parameters per the tables in the following sections. Note that the external parts count can be reduced in some cases by unconnecting or grounding the configuration pins.

Output-Voltage Selection

The SET pin is used to establish the initial output voltage and can be pin strapped high or low, or connected to SGND through a resistor, to select the output voltage, as shown in [Table 1](#). Note that the SET pin is read once at power-up and cannot be used to change the output voltage after that time. Note that shorting SET to ground puts the device into track mode. See the track mode paragraph for more information. The device considers open circuit on SET to be a fault condition so it sets the output voltage to OV to protect the load.

If the desired output voltage is not included in [Table 1](#), use a resistor to set the initial approximate output voltage, and then send VOUT_COMMAND to set the exact desired output voltage.

The output voltage can be set to any voltage between 0.5V and 5.25V, including margining, provided the input voltage to the DC-DC converter (V_{PWR}) is higher than the output voltage by an amount that conforms to the maximum duty-cycle specification.

The device's output voltage can be dynamically changed during operation through several PMBus commands. The output voltage can be decreased during operation without limit. The output voltage can be increased to 20% above the upper end of the allowable voltage determined by the RDIV setting. The RDIV setting is determined by the programmed output voltage when the output is enabled. [Table 5](#) shows the voltage ranges that set each RDIV setting. As an example, if the output voltage is pin strapped to 1.2V, the RDIV is set to 0.65572 at startup. The output voltage can be increased to 15% above the upper end of the 0.65572 RDIV range, or 1.723V. The output voltage can be programmed higher than 1.723V, but the actual power-supply output may be clamped to a lower voltage.

Setting Switching Frequency

The switching frequency can be adjusted from 300kHz to 1MHz with an external resistor from SYNC to SGND per [Table 3](#), or by sending the PMBus FREQUENCY_SWITCH command. Note that the SYNC pin is read once at power-up and cannot be used to change the switching frequency after that time. The device considers open circuit on SYNC to be a fault condition so it sets the switching frequency to 575kHz in an attempt to pick a switching frequency typical of most applications. 575kHz is not a normal pin-strappable frequency, so if the user reads back a switching frequency of 575kHz, they know the SYNC resistor is open circuited. The switching frequency can be changed on the fly for frequencies between 300kHz to 475kHz and for frequencies between 476kHz to 1000kHz. The switching frequency during operation must stay either above or below 475kHz and should never cross this frequency. Doing so may result in unexpected operation. The user can cross the 475kHz switching boundary by disabling the device, changing the switching frequency, and then reenabling the device.

As a guideline, lower frequencies can be used to improve efficiency, while higher frequencies can be selected to reduce the physical size and value of the external filter inductor and capacitors.

Table 1. Output-Voltage Setting Using Pin-Resistor Setting

R _{SET} (kΩ)	OUTPUT VOLTAGE (V)
0 to 4.3	Track mode
5 to 5.2	0.6
6.1 to 6.3	0.7
7 to 7.3	0.75
8.1 to 8.4	0.8
9.4 to 9.7	0.85
10.8 to 11.2	0.9
12.5 to 12.9	0.95
14.5 to 14.9	1
17.6 to 18	1.05
21.2 to 21.8	1.1
25.8 to 26.4	1.2
31.2 to 32	1.5
37.9 to 38.7	1.8
43.7 to 44.7	2.5
50.5 to 51.7	3.3
58.4 to 59.6	5
67.4 to Open	0

External Synchronization

The device can be synchronized with an external clock to eliminate beat noise on the input- and output-voltage lines or to minimize input-voltage ripple. Synchronization is achieved by connecting a clock source to the SYNC pin. The incoming clock signal must be in the 300kHz to 1MHz range and must be stable (see the SYNC Frequency Drift Tolerance specification in the [Electrical Characteristics](#) table). The device synchronizes to the rising edge of the clock after the device is enabled. In the event of a loss of the external clock signal during normal operation after successful synchronization with the external clock, the device automatically switches at the frequency programmed into the PMBus command's FREQUENCY_SWITCH variable. If an external clock is present at power-on when the device is trying to read the SYNC pin-strap resistance, the device cannot detect the synchronization frequency and does not write the proper frequency into FREQUENCY_SWITCH. However, if the clock is still present at enable, the device reads the proper frequency and overwrites FREQUENCY_SWITCH with the actual clock frequency.

Table 2. Interleave Settings

SMBus ADDRESS	PHASE DELAY (°)
xxxx000b	0
xxxx001b	60
xxxx010b	120
xxxx011b	180
xxxx100b	240
xxxx101b	300
xxxx110b	90
xxxx111b	270

If a clock is not present at power-on, the device reads the pin-strap resistor value and writes the frequency into FREQUENCY_SWITCH per [Table 3](#). If an external clock is applied to SYNC after power-on but before enable, the device overwrites FREQUENCY_SWITCH with the external clock frequency when the device is enabled. If an external clock is not applied prior to the device being enabled, the device keeps the originally programmed FREQUENCY_SWITCH value. Applying a clock to SYNC after the device is enabled causes the IC to synchronize to the clock, however, the FREQUENCY_SWITCH value is not updated. For proper synchronization, the external clock can be applied prior to applying power to the device, but must be applied prior to enabling the device. The external clock frequency should not be changed after the device is enabled.

The device supports interleaving with an external SYNC input. The default phase delay is pin strappable and is determined by the 7-bit SMBus address, as shown in [Table 2](#). The phase delay can also be changed by sending the PMBus INTERLEAVE command while the output is disabled. The phase delay should not be changed during operation. The programmed phase delay is between the rising edge of the SYNC clock signal and the center of the device's PWM pulse. The center of the PWM pulse is used for a reference point because the device's PWM pulse is dual-edge modulated.

SMBus Address Selection

The ADDR0 and ADDR1 pins are used in combination to set the SMBus address, as listed in [Table 4a](#). Note that the SMBus specification recommends against using the shaded addresses. The PMBus address cannot be changed after startup. Note that SMBus address also sets the default phase delay for interleaving with an external

Table 3. Switching Frequency Resistor Settings (SYNC)

R _{SYNC} (kΩ)	SWITCHING FREQUENCY (kHz)
0 to 4.3	575
5 to 5.2	300
6.1 to 6.3	350
7 to 7.3	400
8.1 to 8.4	450
9.4 to 9.7	500
10.8 to 11.2	550
12.5 to 12.9	600
14.5 to 14.9	650
17.6 to 18	700
21.2 to 21.8	750
25.8 to 26.4	800
31.2 to 32	850
37.9 to 38.7	900
43.7 to 44.7	950
50.5 to 51.7	1000
58.4 to Open	575

synchronization clock. The ADDR1 resistor also sets the default IOUT_CAL_GAIN.

IOUT_CAL_GAIN Selection

The device allows the user to set a default pinstrapped IOUT_CAL_GAIN at startup. IOUT_CAL_GAIN is the resistance of the current-sense element, which can be either the power inductor's DCR or a discrete current-sense resistor. The device's actual overcurrent trip point is a function of IOUT_CAL_GAIN, the current-sense element's actual resistance, and the value of the IOUT_OC_FAULT_LIMIT. See the output-overcurrent protection paragraph for more information on setting the overcurrent trip point. Setting IOUT_CAL_GAIN is accomplished by pin strapping, connecting a resistor from ADDR1 to SGND, as listed in [Table 4b](#). The user can achieve a more accurate value of IOUT_CAL_GAIN by setting this parameter through the PMBus. Note that ADDR1 is used to set both the PMBus address and IOUT_CAL_GAIN. The user should first determine the desired PMBus address and then choose the appropriate ADDR1 resistor per [Table 4a](#) and [Table 4b](#).

Table 4a. SMBus Address Set by ADDR0, ADDR1 Resistor Connections

DCR	R _{ADDR1} (kΩ)				
4mΩ →	0 to 4.3	5 to 5.2	6.1 to 6.3	7 to 7.3	8.1 to 8.4
8mΩ →	9.4 to 9.7	10.8 to 11.2	12.5 to 12.9	14.5 to 14.9	17.6 to 18
12mΩ →	21.2 to 21.8	25.8 to 26.4	31.2 to 32	37.9 to 38.7	43.7 to 44.7
16mΩ →	50.5 to 51.7	58.4 to 59.6	67.4 to 68.8	85.7 to 87.5	113.8 to 116.2
20mΩ →	138.6 to 141.4	167.3 to 170.7	202.9 to 207.1	234.6 to 239.4	271.2 to Open
R _{ADDR0} (kΩ)	SMBus 7-BIT DEVICE ADDRESS				
0 to 4.3	0x0A	0x22	0x3A	0x52	0x6A
5 to 5.2	0x0B	0x23	0x3B	0x53	0x6B
6.1 to 6.3	0x0C	0x24	0x3C	0x54	0x6C
7 to 7.3	0x0D	0x25	0x3D	0x55	0x6D
8.1 to 8.4	0x0E	0x26	0x3E	0x56	0x6E
9.4 to 9.7	0x0F	0x27	0x3F	0x57	0x6F
10.8 to 11.2	0x10	0x28	0x40	0x58	0x70
12.5 to 12.9	0x11	0x29	0x41	0x59	0x71
14.5 to 14.9	0x12	0x2A	0x42	0x5A	0x72
17.6 to 18	0x13	0x2B	0x43	0x5B	0x73
21.2 to 21.8	0x14	0x2C	0x44	0x5C	0x74
25.8 to 26.4	0x15	0x2D	0x45	0x5D	0x75
31.2 to 32	0x16	0x2E	0x46	0x5E	0x76
37.9 to 38.7	0x17	0x2F	0x47	0x5F	0x77
43.7 to 44.7	0x18	0x30	0x48	0x60	0x78
50.5 to 51.7	0x19	0x31	0x49	0x61	0x79
58.4 to 59.6	0x1A	0x32	0x4A	0x62	0x7A
67.4 to 68.8	0x1B	0x33	0x4B	0x63	0x7B
85.7 to 87.5	0x1C	0x34	0x4C	0x64	0x7C
113.8 to 116.2	0x1D	0x35	0x4D	0x65	0x7D
138.6 to 141.4	0x1E	0x36	0x4E	0x66	0x7E
167.3 to 170.7	0x1F	0x37	0x4F	0x67	0x7F
202.9 to 207.1	0x20	0x38	0x50	0x68	0x7F
234.6 to Open	0x21	0x39	0x51	0x69	0x7F

Note: The SMBus specification recommends against using the shaded addresses.

Table 4b. IOUT_CAL_GAIN Set by ADDR1 Resistor Connection

R _{ADDR1} (kΩ)	IOUT_CAL_GAIN (mΩ)
0 to 8.4	4
9.4 to 18	8
21.2 to 44.7	12
50.5 to 116.2	16
138.6 to Open	20

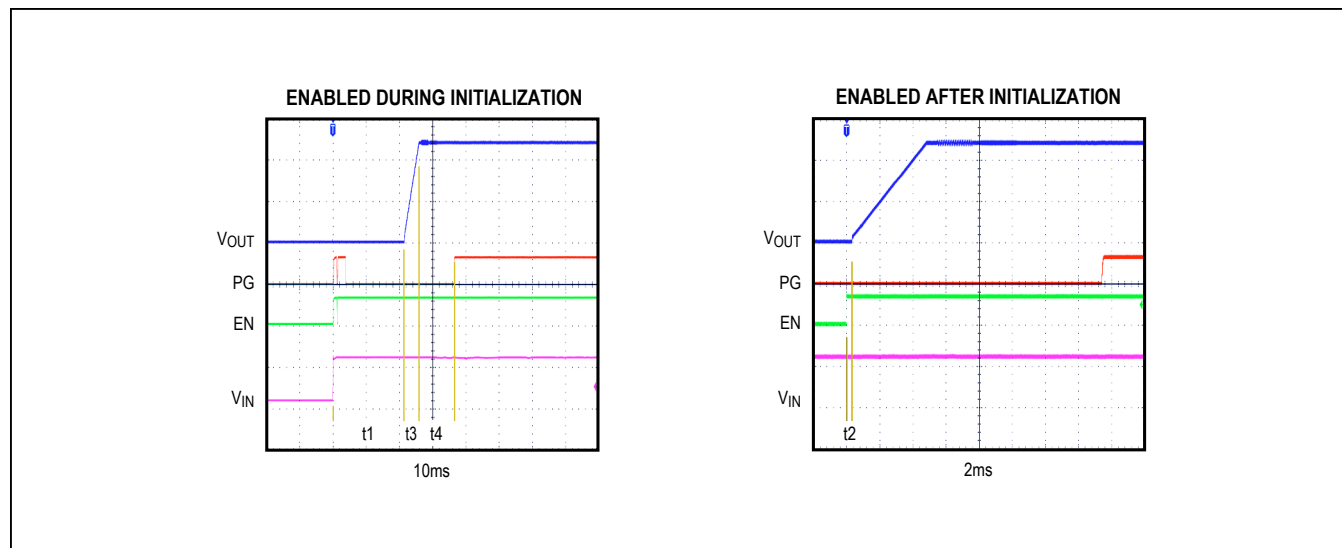


Figure 2. Startup Timing Diagrams

Internal Bias Regulators

The device analog circuitry is powered by an internal 3.3V regulator (3P3). The device also has an internal bias regulator to generate a 1.8V rail (1P8) to power internal digital circuitry. Bypass the 3P3 pin to SGND with a 4.7 μ F ceramic (X5R or better) capacitor. Bypass 1P8 to DGND with a 10 μ F ceramic (X5R or better) capacitor. These internal regulators are not designed to power external circuitry.

Input-Voltage Feed Forward

The device uses input-voltage feed-forward techniques to provide excellent line regulation. Connect the INSNS pin to the power-train input voltage through a 2k Ω series resistor for input-voltage feed-forward and telemetry. The voltage at INSNS is sampled every 4 μ s.

The device does not enable DC-DC conversion if the voltage at INSNS is below the PMBus VIN_UV_FAULT_LIMIT threshold (default 4V) or below the VIN_ON, VIN_OFF limits (default 6V rising and 5.5V falling, respectively.) The user can read back the measured input-voltage value using the PMBus READ_VIN command.

Output On/Off Control

The device features both a hardware-enable input (EN pin) and a PMBus-enable function. The factory default for the enable functions is that the device can be enabled by either an assertion of the hardware EN pin to a logic-high level or by issuing a PMBus-enable command. The enable functionality can be changed using the PMBus

ON_OFF_CONFIG command (see the PMBus specification for details).

Device Initialization

The device includes power-on-reset circuits that monitor the internal bias supplies and the external supply voltage. When all supplies are above their UVLO thresholds, the following self-test sequence occurs:

- 1) Run self-test and CRC check on the memory.
- 2) Read resistor settings and set command values and program working memory accordingly.
- 3) Confirm absence of any faults that would prevent turn-on.
- 4) Begin wait for a valid output-enable condition (hardware or PMBus command).

The power-up and initialization process takes approximately 25ms, depending on the specific combination of pin-strap resistor values to be read. The device does not enable output regulation until initialization is complete.

Output-Voltage Sequencing

In a system with multiple MAX15303 devices or other PMBus-controlled ICs, output-voltage sequencing can be achieved by configuring each power supply with different turn-on/turn-off delays and output rise/fall times. All power supplies are then commanded to turn on (or off) simultaneously using a combined EN signal, or by using the PMBus Group Command Protocol.

The device supports soft-start and soft-stop functionality as shown in [Figure 3](#). The PMBus TON_RISE and TOFF_FALL commands determine the soft-start and soft-stop ramp times. The TON_DELAY command sets the time from a valid enable condition to the beginning of the output-voltage ramp. Similarly, the TOFF_DELAY command sets the time between loss of valid enable condition and the beginning of the output ramp-down to 0V. The default setting for TON_DELAY is the minimum value of 1ms and the default setting for the TON_RISE is 5ms.

The output-voltage slew rates for turn-on and turn-off are given by VOUT_COMMAND/TON_RISE and VOUT_COMMAND/TOFF_FALL, respectively. It is recommended to set TON_RISE and TOFF_FALL to at least 1ms to prevent excessive inrush currents due to high dV/dt. The output-voltage ramp-up rises monotonically above 300mV regardless of input voltage, output voltage, or prebias voltage on the output. Note that the device initiates the InTune calibration process after the soft-start ramp-up is complete.

Startup with Prebias

The device supports soft-start into a prebias output-voltage condition. A prebias condition occurs when there is already a voltage at the output of the power supply before it has been enabled. This can be caused by precharged output capacitors, or a parasitic ESD diode in the load IC that pulls the output up to another system-supply rail. When EN is asserted, the device checks the output for the presence of prebias voltage. If the prebias voltage is less than 200mV, startup is performed normally assuming no prebias. If the prebias is greater than 200mV but below the target set point for the output, the device ramps up the output voltage from the prebias voltage to the regulation set point, as shown in [Figure 4](#). If the prebias is above the VOUT_OV_FAULT_LIMIT value, the device does not attempt soft-start.

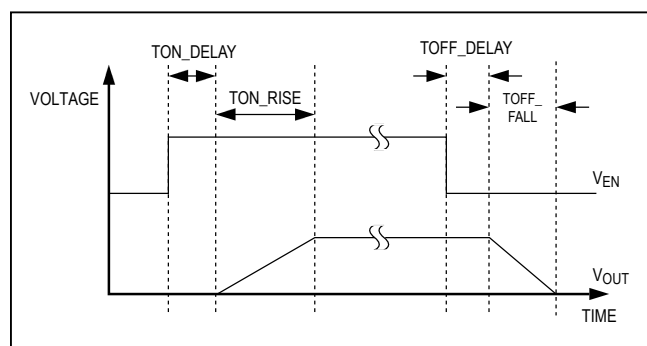


Figure 3. Turn-On/Off Delays and Soft-Start/Stop Times

If prebias was detected at the time of enable, the device saves the prebias voltage level in a register and terminates the output-voltage ramp-down at the pre-bias voltage when disabled. This register is not user accessible.

Voltage Tracking

The device supports voltage tracking of the output from a reference input. To select the tracking mode, connect the SET pin to SGND. The device's output tracks the V_{TRACK} voltage with a preset ratio governed by an internal feedback divider (RDIV) and an external resistive voltage-divider (R1, R2), which is placed from the supply being tracked to SGND ([Figure 5](#)). The center tap of the external divider should be connected to the CIO input.

In tracking mode, V_{OUT} is regulated to the lower of:

$$V_{OUT} = \frac{V_{TRACK}}{RDIV} \times \frac{R1}{R1 + R2}$$

or the output set-point voltage (V_{OUT(SET)}), as determined by the VOUT_COMMAND. As seen in the above equation, if the resistor-divider ratio $RR = R1/(R1 + R2)$ is chosen such that it is equal to the operational RDIV, the output voltage follows the tracking voltage coincidentally ([Figure 6a](#)). For all other cases, the V_{OUT} follows a ratiometric tracking ([Figure 6b](#)) depending on the ratio of RR and RDIV. The IC automatically selects RDIV based on the output set-point voltage as shown in [Table 5](#). For example, if V_{OUT(SET)} is set to 1.6V by the VOUT_COMMAND, RDIV is set to 0.54247. Note that the default RDIV value in track mode is 0.20272, which corresponds to a 5V output-voltage setting. For reliable voltage tracking, it is recommended that once the device is powered up, the VOUT_COMMAND should not be changed so as to cause a change to the operational RDIV ([Table 5](#)). If such a change in VOUT_COMMAND is required, the user should save the new V_{OUT(SET)} in the

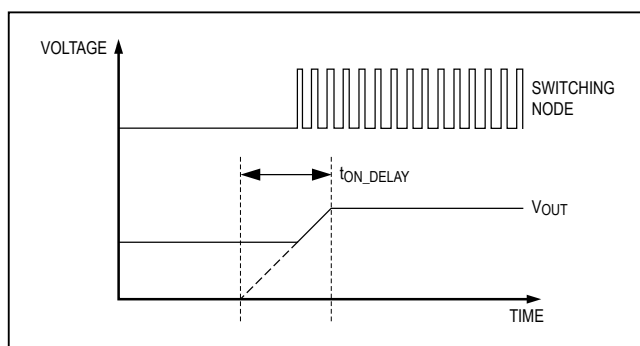


Figure 4. Startup into a Prebiased Output

device memory (using STORE_USER_ALL_COMMAND) and recycle the input power to set a new RDIV operational value. For simplicity, fix R1 at 10kΩ and use the following equation to determine R2:

$$R2 = 10k \times \left(\frac{V_{TRACK}}{R_{DIV} \times V_{OUT}} - 1 \right)$$

For the best voltage regulation, RR should be set such that the final VOUT tracking target voltage is slightly higher than the output set-point voltage determined by VOUT_COMMAND (5V default). The output-voltage ramp tracks the VTRACK input, as shown in Figure 6, until reaching the VOUT_COMMAND value. If the application requires continuous ratiometric tracking, VOUT_COMMAND should be set higher than the desired VOUT tracking target or left at the 5.0V default value. In this case, there is a small regulation inaccuracy due to the tolerance of the external resistors.

Output-Voltage Margining

The device supports voltage margining, which can be used to test the end equipment’s design margin associated with

power-supply variation. The margin set-point commands (VOUT_MARGIN_HIGH and VOUT_MARGIN_LOW) are set to ±5% of VOUT_COMMAND by default, but can be changed through the PMBus interface. Output-voltage margining is controlled by the OPERATION command.

Table 5. Required Divider Ratio (RDIV) as a Function of VOUT

VOUT_COMMAND (V)	RDIV
< 0.55	0.99547
0.55 to < 0.95	0.88222
0.95 to < 1.15	0.76897
1.15 to < 1.502	0.65572
1.502 to < 1.815	0.54247
1.815 to < 2.295	0.42922
2.295 to < 3.117	0.31597
3.117 to < 5.5	0.20272

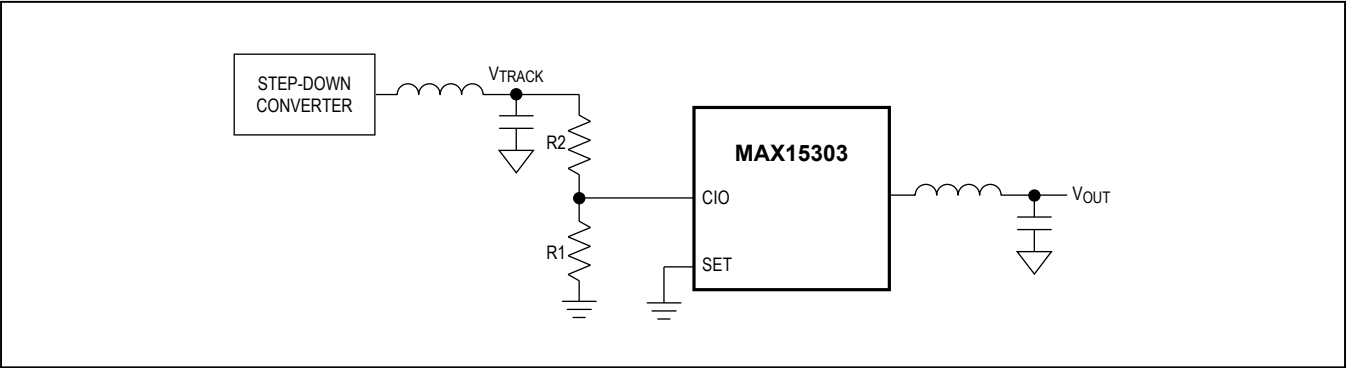


Figure 5. Tracking Mode Configuration

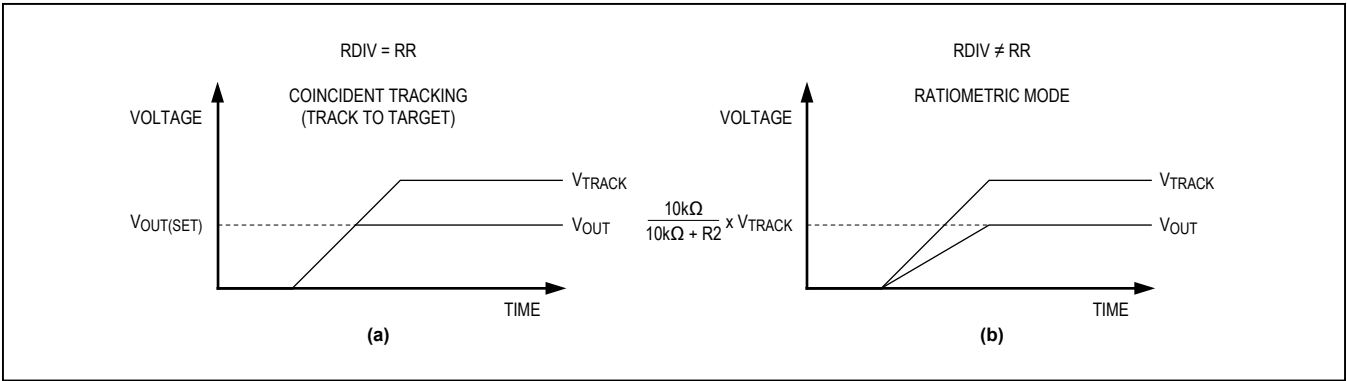


Figure 6. Tracking

Output Voltage Ranges and Fault Limits

The device features output undervoltage and overvoltage protection. The PMBus VOUT_OV_FAULT_LIMIT is set to 115% of VOUT_COMMAND by default, and VOUT_UV_FAULT_LIMIT is set to 85%. These thresholds can be changed through PMBus and set anywhere between 0V and the lower of either the ADC full-scale value or VOUT_MAX (VOUT_MAX is 110% of VOUT_COMMAND by default).

The device continuously monitors the output voltage. If the voltage exceeds the protection limits, the device follows the actions prescribed by the VOUT_OV_FAULT_RESPONSE or VOUT_UV_FAULT_RESPONSE commands as appropriate. By default, an overvoltage fault results in an immediate shutdown with no retry attempts, whereas an undervoltage fault is ignored. The fault response commands can be changed at any time, but changes to the fault-response commands only take effect when the output is disabled.

Output-Overcurrent Protection

The MAX15303 monitors the voltage across the output inductor resistance (or other resistive sense element) to provide output-current monitoring and overload protection. The voltage signal at the current-sense element is divided by the IOUT_CAL_GAIN value to yield output current in amps. The value of IOUT_CAL_GAIN is initially set by the ADDR1 resistance, according to [Table 4b](#), and should be set as close as possible to the inductor DCR (or the resistive sense element's resistance). More accurate output-current measurement can be achieved by calibrating the IOUT_CAL_GAIN value. For more information on calibrating IOUT_CAL_GAIN, refer to Maxim Application Note #AN5601: *Current Calibration Procedure for InTune Digital Power*.

The overcurrent-fault threshold is set by the IOUT_OC_FAULT_LIMIT command; the default value is 8A. The default fault response to an overcurrent condition is to turn off both internal MOSFETs, wait 700ms, and then restart the regulator. This process repeats indefinitely until the fault condition no longer persists. This fault-response behavior can be changed using the PMBus IOUT_OC_FAULT_RESPONSE command.

Fault Handling

The device monitors input voltage, output voltage, output current, and both internal and external temperatures. The fault thresholds and responses are factory-set, but can be changed using PMBus commands. Fault detection can be

individually enabled or disabled for the parameters through the PMBus. The default limits are as indicated in [Table 6](#). The response to a fault condition can be changed through the PMBus. Refer to Maxim Application Note #AN5816 *MAX15303 PMBus Command Set User's Guide* for more information on setting fault thresholds and fault responses.

Nonvolatile PMBus Memory

The device includes three nonvolatile memory banks to store PMBus configuration values. The first is the MAXIM store, which contains a read-only copy of all default command settings. The next is the read/write-accessible DEFAULT store, which is intended to contain an equipment manufacturer's preferred or suggested settings. Third is the read/write-accessible USER store, which is intended to store the end user's preferred settings.

When the device is enabled, a combination of the pin-configurable command values and the contents of the USER store are loaded into working memory. Any command values that have been edited and stored to the USER memory take precedence over their corresponding pin-configured values.

Equipment manufacturers should ensure that the DEFAULT and USER stores are saved with duplicate copies of the manufacturer's preferred or suggested command values. In this manner, an end user can restore the DEFAULT memory and save to the USER store any time they wish to return the device to the manufacturer's original configuration.

Special security commands and features are included so that a manufacturer user can store and lock the regulator's configuration on a command-by-command basis. Contact Maxim for application notes describing these security features.

Table 6. Fault Conditions

FAULT CONDITION	DEFAULT THRESHOLD	RANGE
V _{IN} Overvoltage	14V	0 to 14.7V
V _{IN} Undervoltage	4.2V	0 to 14.7V
V _{OUT} Overvoltage	VOUT_COMMAND x 115%	0 to 5.5V
V _{OUT} Undervoltage	VOUT_COMMAND x 85%	0 to 5.5V
I _{OUT} Overcurrent	8A	0 to 8.97A
Overtemperature	115°C	-40°C to +150°C

Temperature Sensing

The device supports remote temperature sensing in addition to sensing its own internal temperature. The device uses a ΔV_{BE} measurement internally and at the TEMPX input to compute temperature. This technique is widely employed because it requires no calibration of the sensor. Any PN junction can be used as a temperature sensor. The 2N3904, 2N2222 transistors and integrated thermal diodes found in microprocessors, FPGAs, and ASICs are commonly used temperature sensors. Connect a 100pF filter capacitor, as shown in [Figure 7](#), to ensure accurate temperature measurements.

The device temperature and thermal-fault thresholds are programmed through the PMBus interface. The default value for the thermal-shutdown threshold is +115°C. The device shuts down and PG pulls low when it crosses the temperature-fault threshold.

Power Good (PG)

PG is an open-drain power-good output used to indicate when the device is ready to provide regulated output voltage to the load. During startup and during a fault condition, PG is held low. PG is asserted high after the output has ramped to a voltage above the POWER_GOOD_ON threshold and a successful InTune calibration has completed. If the output regulation voltage falls below the POWER_GOOD_OFF threshold, PG is deasserted.

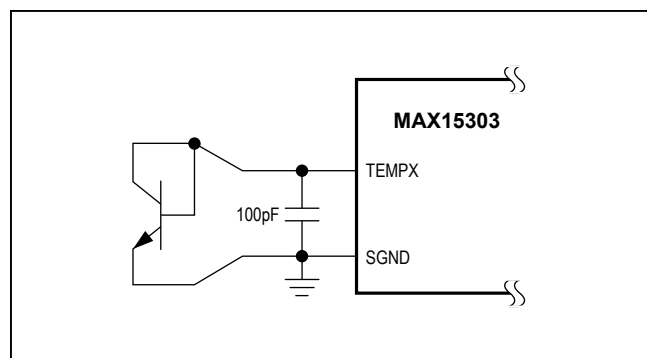


Figure 7. Temperature Sensing with a 2N3904 npn Transistor

PMBus Digital Interface

The MAX15303 is a PMBus-compatible device that includes many of the standard PMBus commands. A PMBus 1.2-compliant device uses the System Management Bus (SMBus) version 2.0 for transport protocol and responds to the SMBus slave address. In this data sheet, the term SMBus is used to refer to the electrical characteristics of the PMBus communication using the SMBus physical layer. The term PMBus is used to refer to the PMBus command protocol.

The device employs six standard SMBus protocols (Write Byte, Read Byte, Write Word, Read Word, Write Block, and Read Block) to program output voltage and warning/faults thresholds, read monitored data, and provide access to all manufacturer-specific commands.

The device also supports the group command. The group command is used to send commands to more than one PMBus device. It is not required that all the devices receive the same command. However, no more than one command can be sent to any one device in one group command packet. The group command must not be used with commands that require the receiving device to respond with data, such as the STATUS_BYTE command. When the device receives a command through this protocol, it begins execution immediately of the received command after detecting the STOP condition.

When the data word is transmitted, the lower order byte is sent first and the higher order byte is sent last. Within any byte, the most significant bit (MSB) is sent first and the least significant bit (LSB) is sent last. Contact the factory for detailed PMBus command support.

Supported PMBus Commands

The device supports the standard PMBus commands given in [Table 7](#). Refer to Maxim Application Note AN5816: *MAX15303 PMBus Command Set User's Guide* for the device's PMBus command details.

A single pair of pullup resistors (one each for SCL and SDA) is required for each shared bus, as shown in [Figure 8](#). Consult the SMBus 2.0 specifications as well as the guaranteed drive capability of SDA in the

Table 7. PMBus Command Summary

COMMAND CODE	COMMAND NAME	SMBus TRANSFER TYPE	# OF DATA BYTES	MIN	MAX	DEFAULT VALUE	UNITS
0x01	OPERATION	R/W Byte	1	—	—	0x40	—
0x02	ON_OFF_CONFIG	R/W Byte	1	—	—	0x16	—
0x03	CLEAR_FAULTS	Send Byte	0	—	—	—	—
0x10	WRITE_PROTECT	R/W Byte	1	—	—	0	—
0x11	STORE_DEFAULT_ALL	Send Byte	0	—	—	—	—
0x12	RESTORE_DEFAULT_ALL	Send Byte	0	—	—	—	—
0x15	STORE_USER_ALL	Send Byte	0	—	—	—	—
0x16	RESTORE_USER_ALL	Send Byte	0	—	—	—	—
0x19	CAPABILITY	Read Byte	1	—	—	0xA0	—
0x20	VOUT_MODE	Read Byte	1	—	—	0x14	—
0x21	VOUT_COMMAND	R/W Word	2	0.5	5.25	SET pin resistor setting	V
0x22	VOUT_TRIM	R/W Word	2	—	—	0	V
0x23	VOUT_CAL_OFFSET	R/W Word	2	—	—	0	V
0x24	VOUT_MAX	R/W Word	2	—	—	VOUT_COMMAND + 10%	V
0x25	VOUT_MARGIN_HIGH	R/W Word	2	—	—	VOUT_COMMAND + 5%	V
0x26	VOUT_MARGIN_LOW	R/W Word	2	—	—	VOUT_COMMAND - 5%	V
0x27	VOUT_TRANSITION_RATE	R/W Word	2	—	—	0.1	mV/μs
0x28	VOUT_DROOP	R/W Word	2	—	—	0	mΩ
0x33	FREQUENCY_SWITCH	R/W Word	2	300	1000	SYNC pin resistor setting	kHz
0x35	VIN_ON	R/W Word	2	4	12	6	V
0x36	VIN_OFF	R/W Word	2	4	12	5.5	V
0x37	INTERLEAVE	R/W Word	2	—	—	See Table 2	—
0x38	IOUT_CAL_GAIN	R/W Word	2	—	—	ADDR1 pin resistor setting	mΩ
0x39	IOUT_CAL_OFFSET	R/W Word	2	—	—	0	A
0x40	VOUT_OV_FAULT_LIMIT	R/W Word	2	—	—	VOUT_COMMAND + 15%	V
0x41	VOUT_OV_FAULT_RESPONSE	R/W Byte	1	—	—	0x80	—
0x44	VOUT_UV_FAULT_LIMIT	R/W Word	2	—	—	VOUT_COMMAND - 15%	V
0x45	VOUT_UV_FAULT_RESPONSE	R/W Byte	1	—	—	0x00	—
0x46	IOUT_OC_FAULT_LIMIT	R/W Word	2	—	—	8	A
0x47	IOUT_OC_FAULT_RESPONSE	R/W Byte	1	—	—	0xBF	—
0x4F	OT_FAULT_LIMIT	R/W Word	2	—	—	115	°C
0x50	OT_FAULT_RESPONSE	R/W Byte	1	—	—	0xC0	—
0x51	OT_WARN_LIMIT	R/W Word	2	—	—	95	°C

Table 7. PMBus Command Summary (continued)

COMMAND CODE	COMMAND NAME	SMBus TRANSFER TYPE	# OF DATA BYTES	MIN	MAX	DEFAULT VALUE	UNITS
0x55	VIN_OV_FAULT_LIMIT	R/W Word	2	—	—	14	V
0x56	VIN_OV_FAULT_RESPONSE	R/W Byte	1	—	—	0xC0	—
0x59	VIN_UV_FAULT_LIMIT	R/W Word	2	—	—	4.2	V
0x5A	VIN_UV_FAULT_RESPONSE	R/W Byte	1	—	—	0xC0	—
0x5E	POWER_GOOD_ON	R/W Word	2	—	—	VOUT_COMMAND - 10%	V
0x5F	POWER_GOOD_OFF	R/W Word	2	—	—	VOUT_COMMAND - 15%	V
0x60	TON_DELAY	R/W Word	2	—	—	5	ms
0x61	TON_RISE	R/W Word	2	—	—	5	ms
0x64	TOFF_DELAY	R/W Word	2	—	—	1	ms
0x65	TOFF_FALL	R/W Word	2	—	—	5	ms
0x78	STATUS_BYTE	Read Byte	1	—	—	—	—
0x79	STATUS_WORD	Read Word	2	—	—	—	—
0x7A	STATUS_VOUT	Read Byte	1	—	—	—	—
0x7B	STATUS_IOUT	Read Byte	1	—	—	—	—
0x7C	STATUS_INPUT	Read Byte	1	—	—	—	—
0x7D	STATUS_TEMPERATURE	Read Byte	1	—	—	—	—
0x7E	STATUS_CML	Read Byte	1	—	—	—	—
0x88	READ_VIN	Read Word	2	—	—	—	V
0x8B	READ_VOUT	Read Word	2	—	—	—	V
0x8C	READ_IOUT	Read Word	2	—	—	—	A
0x8D	READ_TEMPERATURE_1	Read Word	2	—	—	—	°C
0x8E	READ_TEMPERATURE_2	Read Word	2	—	—	—	°C
0x94	READ_DUTY_CYCLE	Read Word	2	—	—	—	%
0x95	READ_FREQUENCY	Read Word	2	—	—	—	kHz
0x98	PMBUS_REVISION	Read Byte	1	—	—	0x22	—
0x99	MFR_ID	R/W Block	8	—	—	null	—
0x9A	MFR_MODEL	R/W Block	13	—	—	null	—
0x9B	MFR_REVISION	R/W Block	7	—	—	null	—
0x9C	MFR_LOCATION	R/W Block	8	—	—	null	—
0x9D	MFR_DATE	R/W Block	6	—	—	null	—
0x9E	MFR_SERIAL	R/W Block	13	—	—	null	—
0xAD	IC_DEVICE_ID	Read Block	8	—	—	"MAX15303"	—
0xAE	IC_DEVICE_REV	Read Word	2	—	—	<firmware revision>	—

Table 7. PMBus Command Summary (continued)

COMMAND CODE	COMMAND NAME	SMBus TRANSFER TYPE	# OF DATA BYTES	MIN	MAX	DEFAULT VALUE	UNITS
0xD0	ADAPTIVE_MODE	R/W Word	2	—	—	0x024B	—
0xD3	FEEDBACK_EFFORT	R/W Word	2	—	—	0.5	—
0xD5	LOOP_CONFIG	R/W Word	2	—	—	0x0100	—
0xDB	COMP_MODEL	R/W Block	6	—	—	0.025, 0.41666, 1.0	—
0xE0	MANUF_CONF	R/W Block	32	—	—	0	—
0xE1	MANUF_LOCK	Write Word	2	—	—	0	—
0xE2	MANUF_PASSWD	R/W Word	2	—	—	0	—
0xE3	USER_CONF	R/W Block	32	—	—	0	—
0xE4	USER_LOCK	Write Word	2	—	—	0	—
0xE5	USER_PASSWD	R/W Word	2	—	—	0	—
0xE6	SECURITY_LEVEL	Read Byte	1	—	—	0x00	—
0xE7	DEADTIME_GCTRL	R/W Block	19	—	—	See PMBus Application Note	—
0xE8	ZETAP	R/W Word	2	—	—	1.5	—
0xEA	RESTORE_MAXIM_ALL	Send Byte	0	—	—	—	—
0xF8	EXT_TEMP_CAL	R/W Block	6	—	—	0.0040, -8, 0.0038	none °K, 1/°

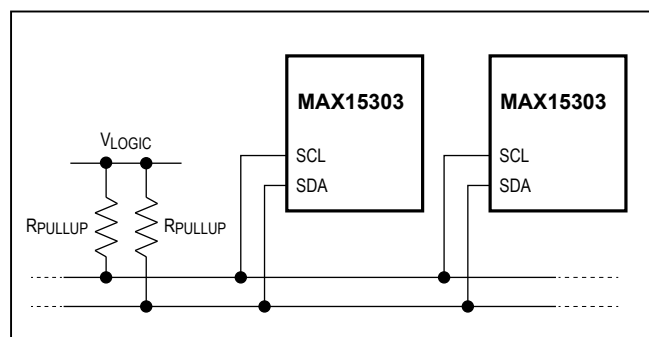


Figure 8. SMBus Multidevice Configuration

[Electrical Characteristics](#) table to determine the value of the pullup resistors.

Design Procedure

The following paragraphs provide details for designing a MAX15303-based power supply. The first step is to ensure the device meets the system-level input and output voltage range. If these requirements are met, the detailed design can begin.

Maximum Output Current

The device's internal switching FETs limit the maximum allowable output current to 6A. For some extreme operating conditions, the maximum allowable output current may be less than 6A. The High-Side nMOS's average must be less than the 4.3A limitation in the [Electrical Characteristics](#) table. Note that this 4.3A maximum average-current limitation only prohibits 6A operation in very high duty-cycle cases. The MAX15303 maximum output current is the lower of either 6A or the value defined by the following equation:

$$I_{OUTMAX} < 4.3A \times V_{IN}/V_{OUT}$$

Switching-Frequency Selection

The first step in selecting a buck controller's output filter is to select the desired switching frequency (f_{SW}) for the PWM. The device offers ability to adjust switching frequency from 300kHz to 1MHz. The choice of switching frequency requires a trade-off between efficiency and solution size. Select a low frequency for higher efficiency. Use a higher frequency to reduce the size of the external filter components and to improve transient response. Also consider system frequency requirements

when choosing f_{SW} , such that the harmonics of the switching frequencies do not interfere with the system operation. The switching frequency for the device is set by the SYNC pin connection per [Table 3](#).

The switching frequency can be changed through the FREQUENCY_SWITCH PMBus command at any time the controller is disabled. The default value of 600kHz provides a good balance of efficiency, small size, and good transient response.

Inductor Selection

Three key inductor parameters must be specified to select an inductor for operation with the device: inductance value (L), inductor saturation current (I_{SAT}), and maximum DC resistance (DCR).

- 1) Inductor value selection: For automatic compensation using InTune technology, select the inductor such that the peak-to-peak inductor ripple current (LIR) is 20% to 40% of the maximum operating current (I_{OUTMAX}). Using a low LIR ratio results in higher inductor value. Typically, inductor resistance is proportional to inductance for a given package type, so selecting a lower LIR value results in higher DCR losses and decreases efficiency. Using a high value of LIR increases the RMS current, which also decreases efficiency. Maxim recommends approximately 30% for a peak-to-peak ripple to maximum operating current ratio ($LIR = 0.3$).

The nominal inductor value can now be calculated using LIR, f_{SW} , V_{IN} , V_{OUT} , and I_{OUTMAX} (the maximum DC load current) using the following equation:

$$L = \frac{V_{OUT}(V_{IN} - V_{OUT})}{V_{IN} f_{SW} I_{OUT} LIR}$$

$$0.2 \leq LIR \leq 0.4$$

The exact inductor value in this range is not critical and can be adjusted to make trade-offs among size, cost, and efficiency. A higher inductance can increase efficiency by reducing the RMS current. Lower inductor values minimize size and cost. Lower inductor values can also improve transient response but reduce efficiency due to higher peak currents.

- 2) The selected inductor's saturation current rating (I_{SAT}) must exceed the user-defined current limit. I_{SAT} should generally be selected such that it is greater than $I_{LIM} + LIR/2 + 10\%$ to provide adequate margin

in the event of a large load transient. It is important to select an inductor that has a high enough I_{SAT} to satisfy this requirement, though this parameter typically forces a certain dimension of inductor to be used.

- 3) Finally, the user should select an inductor with minimal DCR (DC series resistance) to reduce overall losses in efficiency. See the current-sense selection paragraph for more information on selecting the inductor DCR.

Output Capacitor Selection

The device has been optimized to operate with low-ESR output capacitors. These capacitors typically have X5R or X7R dielectrics. High-ESR capacitors can be added, but would provide little benefit to system performance. The output capacitor requirement is dependent upon two considerations:

- 1) Output ripple voltage.
- 2) Load current transient envelope.

Both requirements are easily achieved with all-ceramic output capacitors.

The total output-voltage ripple is a function of the output capacitor's ESR and capacitance and typically chosen to be ~1% of the output voltage. For typical applications, the ripple voltage is dominated by the capacitance. The following equations calculate the minimum output capacitance and maximum allowable ESR:

$$ESR_{MAX} = \frac{V_{RIPPLE}}{\Delta I}$$

$$C_{OUTMIN} = \frac{\Delta I}{8 \times V_{RIPPLE} \times f_{SW}}$$

where ΔI is:

$$\Delta I = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L}$$

The worst case output voltage ripple is:

$$V_{RIPPLE} = \Delta I \times \left(\frac{1}{8 \times C_{OUT} \times f_{SW}} + ESR \right)$$

An ESR below 10mΩ is typically required. The use of two or more 100μF ceramic capacitors in parallel is typically sufficient to achieve a good ripple voltage.

When all-ceramic output capacitors are used, load current transient envelope is the primary concern for capacitor selection. Designs with small load transients can use fewer capacitors and designs with larger load transients require more load capacitance to reduce output “sag” and “soar.” The allowable deviation of the output voltage during fast load transient determines the output capacitance. The following two equations calculate the minimum capacitance required to meet the voltage sag and soar requirements from a load transient:

$$C_{OUT} = \frac{L \times \Delta I^2}{2 \times \Delta V_{SAG} \times (V_{IN} - V_O)} + \frac{\Delta I_O}{2 \times \pi \times BW \times \Delta V_{SAG}}$$

$$C_{OUT} = \frac{L \times \Delta I^2}{2 \times \Delta V_{SOAR} \times V_O} + \frac{\Delta I_O}{2 \times \pi \times BW \times \Delta V_{SOAR}}$$

where BW is the power-supply crossover frequency in Hz, which is approximately $f_{SW}/10$ for the device and C_{OUT} is the output capacitance.

Compensating the Power Supply

Unlike most power-supply designs, the device does not require designing and testing a compensation circuit. The device automatically measures the output filter's resonant frequency and uses this information to set the appropriate compensation parameters. The device is stable if the output-filter corner frequency meets the following requirements:

$$45 \leq f_{SW}/f_{LC} \leq 90$$

where:

$$f_{LC} \doteq 1/(2\pi\sqrt{LC})$$

therefore:

$$\frac{1}{L} \left(\frac{45}{2\pi f_{SW}} \right)^2 \leq C \leq \frac{1}{L} \left(\frac{90}{2\pi f_{SW}} \right)^2$$

Most 600kHz device POL designs are satisfied using a capacitor between 100μF to 500μF of ceramic output capacitance and no additional electrolytic capacitors. The InTune adaptive compensation permits a large range of output inductors and capacitors.

Input Capacitor Selection

The input filter capacitor reduces peak current drawn from the power source and reduces noise and voltage ripple on the input caused by the switching circuitry. The value of the input capacitor is selected to limit the ripple voltage (ΔV) as follows:

$$C_{IN} \geq \frac{I_{OUT} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}} \right)}{f_{SW} \times \Delta V}$$

where ΔV is the required input ripple voltage. This calculation assumes there is measurable inductance back to the original V_{IN} source; thus, this calculation provides low source impedance at the input of the DC-DC converter. The capacitance requirement is greatest when the duty cycle is 50% and decreases as duty cycle increases or decreases.

The input capacitor must meet the ripple-current requirement (I_{RMS}) imposed by the switching currents, as defined by the following equation:

$$I_{RMS} = I_{LOAD(MAX)} \frac{\sqrt{V_{OUT}(V_{IN} - V_{OUT})}}{V_{IN}}$$

I_{RMS} attains a maximum value when the input voltage equals twice the output voltage ($V_{IN} = 2V_{OUT}$), so $I_{RMS(MAX)} = I_{LOAD(MAX)}/2$. For most applications, nontantalum capacitors (ceramic, aluminum, polymer, or OS-CON) are preferred at the inputs due to the robustness of nontantalum capacitors to accommodate high inrush currents of systems being powered from very low impedance sources. Additionally, two (or more) smaller-value low-ESR capacitors can be connected in parallel to reduce high-frequency noise.

Current-Sense Selection

The device uses lossless DCR current sensing to reduce the overall power dissipation and improve efficiency. Lossless sensing is configured by connecting a series RC circuit across the inductor, as shown in [Figure 9](#). Select the resistor and capacitor such that their time constant is equal to that of the inductor and its DCR:

$$R_L C_L = \frac{L}{DCR}$$

Use the typical inductance and DCR values provided by the inductor manufacturer. The resistor value should be set to 2kΩ. Use high-accuracy and low-tempco C0G ceramic capacitors for C_L . Carefully observe the PCB layout guidelines provided in the data sheet to ensure the noise and DC errors do not corrupt the differential current-sense signals seen by DCRP and DCRN. Place the RC network close to the inductor and Kelvin sense the voltage across the capacitor.

The maximum sense voltage produced using lossless sensing is:

$$V_{DCRP} - V_{DCRN} = DCR \times I_{OUT(MAX)}$$

Choose the DCR so the maximum current-sense voltage is between 10mV and 150mV. A higher current sense voltage improves the measurement signal to noise ratio, but increases power dissipation.

More accurate current sensing can be achieved by sensing across a current-sense resistor placed between the inductor and the output capacitors. A dedicated current-sense resistor provides a more accurate resistance and lower tempco than sensing across the inductor. If using a current-sense resistor, connect DCRP to the node between the inductor and the current-sense resistor. Connect DCRN to the node between the current-sense resistor and the output capacitors. Be sure to use Kelvin sensing across the resistor.

For accurate current sensing, program the device's IOUT_CAL_GAIN to be equal to the current-sense element's resistance. Note that the default IOUT_CAL_GAIN is set by the pin-strap resistor connected between ADDR1 and SGND. This default IOUT_CAL_GAIN can be change through the PMBus. If IOUT_CAL_GAIN is not configured to match the actual current-sense resistance, the actual load current is scaled from the measured current by the ratio of IOUT_CAL_GAIN to DCR. In this case, the actual load current is:

$$I_{LOAD} = READ_IOUT \times IOUT_CAL_GAIN / DCR$$

As an example, if IOUT_CAL_GAIN is pin strapped to 10mΩ, the actual inductor DCR is 20mΩ, and a PMBus READ_IOUT command returns 3A; the actual load current is 1.5A.

Boost Capacitor

The device uses a bootstrap circuit to generate the necessary gate-to-source voltage to turn on the high-side MOSFET. The High-Side nMOS is internal to the IC, therefore the boost capacitor can be fixed for all designs. The MAX15303 boost capacitor should be a 0.22μF low-ESR ceramic capacitor.

Selecting Temperature Measurement

The device's external temperature-sensing transistor should be placed near the current-sense element (inductor or current sense resistor) so the device can adjust for variations in resistance versus temperature. A 100pF capacitor can be placed between TEMPX and SGND to reduce noise and improve the accuracy of the temperature measurement. The TEMPX and SGND con-

nections to the transistor should be Kelvin sensed. The device's default temperature-measurement parameters are designed to be used with a Fairchild MMBT3904. If another transistor is used, check with the vendor to get the correct parameters. The default temperature-coefficient setting is 3800ppm/°C, which is the thermal coefficient of copper. This value is appropriate for inductors with copper windings. If a current-sense resistor is used, the temperature coefficient should be changed to match the resistor's value. The default temperature-measurement parameters can be changed through the EXT_TEMP_CAL PMBus command.

Setting Current Limit

The device provides current protection utilizing inductor DCR current sense or a current-sense resistor. The details for selecting the current-sense element are described in the previous paragraph. When the measured current equals the IOUT_FAULT_LIMIT, the device acts on the current faults, as defined by the PMBus IOUT_OC_FAULT_RESPONSE setting. For the most accurate current sensing, configure IOUT_CAL_GAIN through the PMBus to equal the current-sense element. If only the pin-strapped values of IOUT_CAL_GAIN are used, select the R_ADDR1 resistor such that:

$$IOUT_CAL_GAIN \geq DCR \times I_{OUT(MAX)} / 8A$$

Output-Voltage Remote Sensing

The device uses two dedicated inputs (OUTP and OUTN) for the output differential voltage sensing to reduce the common-mode noise sensitivity. This sensing circuitry is part of the feedback loop. The output voltage is connected to the device directly through these two inputs, without the need for an external resistive divider. The PCB traces to

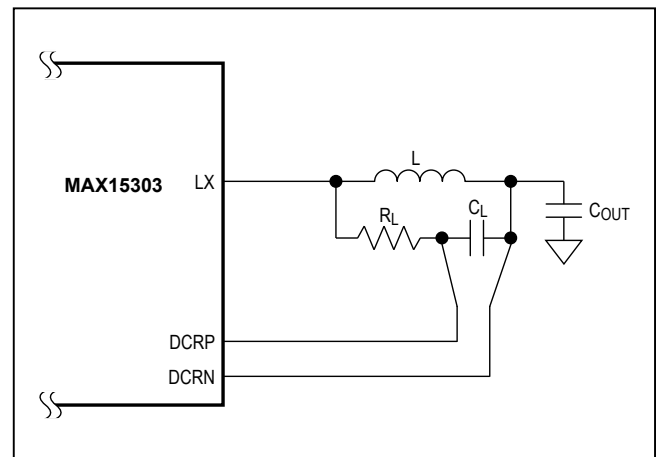


Figure 9. Lossless DCR Current Sensing

the OUTP and OUTN pins should be routed as a differential pair to the desired regulation sense point to minimize noise induced in the sensed signal. A 100pF-1000pF capacitor can be placed directly across OUTP to OUTN to minimize noise.

BabyBuck Component Selection

The device features an internal DC-DC switching regulator to power internal circuitry and provide the gate-drive voltage for the external MOSFETs. Competing parts with internal driver circuits use linear regulators to provide these voltages, which leads to significant efficiency loss when operating from an input voltage above ~6V. The patent-pending BabyBuck circuit improves overall efficiency in a typical application by more than 1% at full load and more than 10% in lightly loaded conditions.

The BabyBuck uses a tiny (1008 size) low-current inductor connected across LBI and LBO (Figure 10). A 10µH inductor with a saturation rating of at least 200mA is recommended for BabyBuck. A 2.2µF ceramic capacitor should be connected from GDRV to PGND.

For applications where efficiency is not critical, the inductor can be omitted and the BabyBuck automatically operates as a linear regulator (Figure 11). In this configuration, bypass GDRV to PGND with a 2.2µF ceramic capacitor and connect LBI to PWR through a 100kΩ resistor. PWR should always be bypassed to PGND with a 1µF ceramic capacitor.

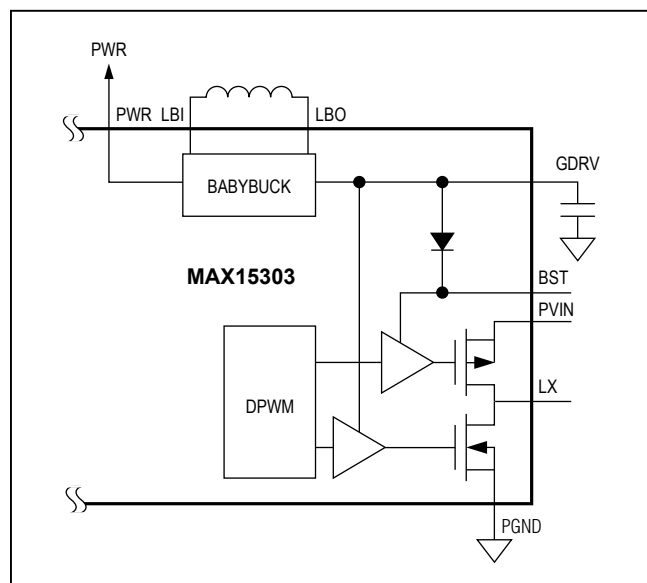


Figure 10. Gate Drivers Powered by Switching Regulator

PMBus Address and Pullup Selection

Select the resistors for ADDR0 and ADDR1 per Table 4a to set the chosen PMBus address. Note that the ADDR1 resistor also sets the default IOUT_CAL_GAIN. Be sure there are no other ICs with the same PMBus address.

SDA and SCL are open-collector input/outputs and must be pulled up to 2.5V or 3.3V. The appropriate pullup-resistor values and location depend on several system-level requirements such as how many other devices are on the bus, the total bus capacitance, the drive strength of each component on the bus, etc.

Schottky Diode

When the device turns off by immediately stopping the switching of both top and bottom FETs, the load current flows through the bottom FET's body diode, pulling the LX voltage below ground. If turnoff occurs with a high load, LX goes low enough to inject current into the IC substrate, potentially causing the IC to reboot. Placing a Schottky diode between LX and PGND prevents the IC from rebooting. The diode should have a forward voltage drop of less than 0.6V at the load's maximum rated current. Note that no current flows through the diode in normal operation. The MBR120 has been used for this function.

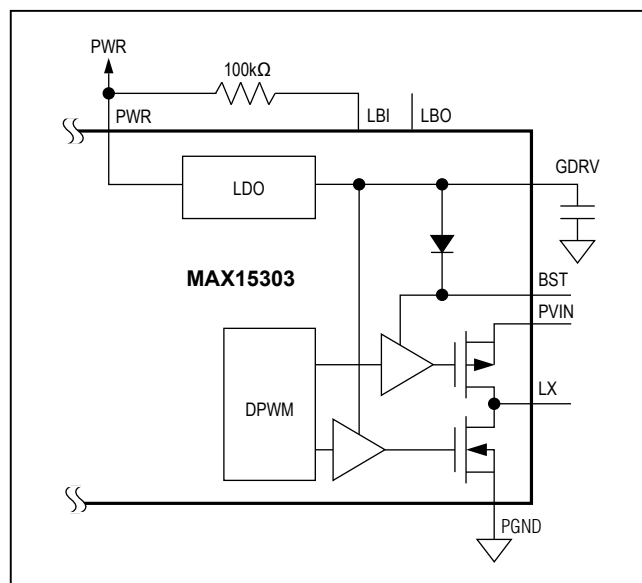


Figure 11. Gate Drivers Powered by Linear Regulator

Design Examples

See [Table 8](#) for the component values in the [Typical Operating Circuit](#). For additional examples and detailed layout information, refer to the MAX15303 evaluation kit.

Applications Information

PCB Layout Guidelines

Careful PCB layout is critical to achieve clean and stable operation. The switching power stage requires particular attention. The MAX15303 evaluation kit provides a known working layout. As a summary, follow these guidelines for best thermal performance and signal integrity:

- 1) When using a resistor to set a command value, connect its return terminal to SGND.
- 2) Connect the power-ground plane (connected to PGND), digital return (connected to DGND), and analog-ground plane (SGND) at one point near the device.
- 3) Bypass GDRV to PGND, 3P3 to SGND, and 1P8 to DGND with ceramic decoupling capacitors. Place the capacitors as close as possible to the pins.
- 4) Minimize the length of the high-current loop from PVIN to the input capacitor to PGND. This is best achieved by using two input capacitors and placing them as shown in the MAX15303 evaluation kit data sheet.
- 5) Provide enough copper area at and around the LX pin to the output inductor and on PGND to help remove power from the internal switching MOSFETs. Maintain a good balance between the LX copper area for thermal performance and electromagnetic radiation.
- 6) Route high-speed switching nodes (BST and LX) away from sensitive sense inputs (OUTP, OUTN, DCRP, DCRN, TEMPX).
- 7) Route the DCRP, DCRN and OUTP, OUTN traces as differential pairs.
- 8) Minimize the length of the traces between LX to the Schottky diode to PGND.

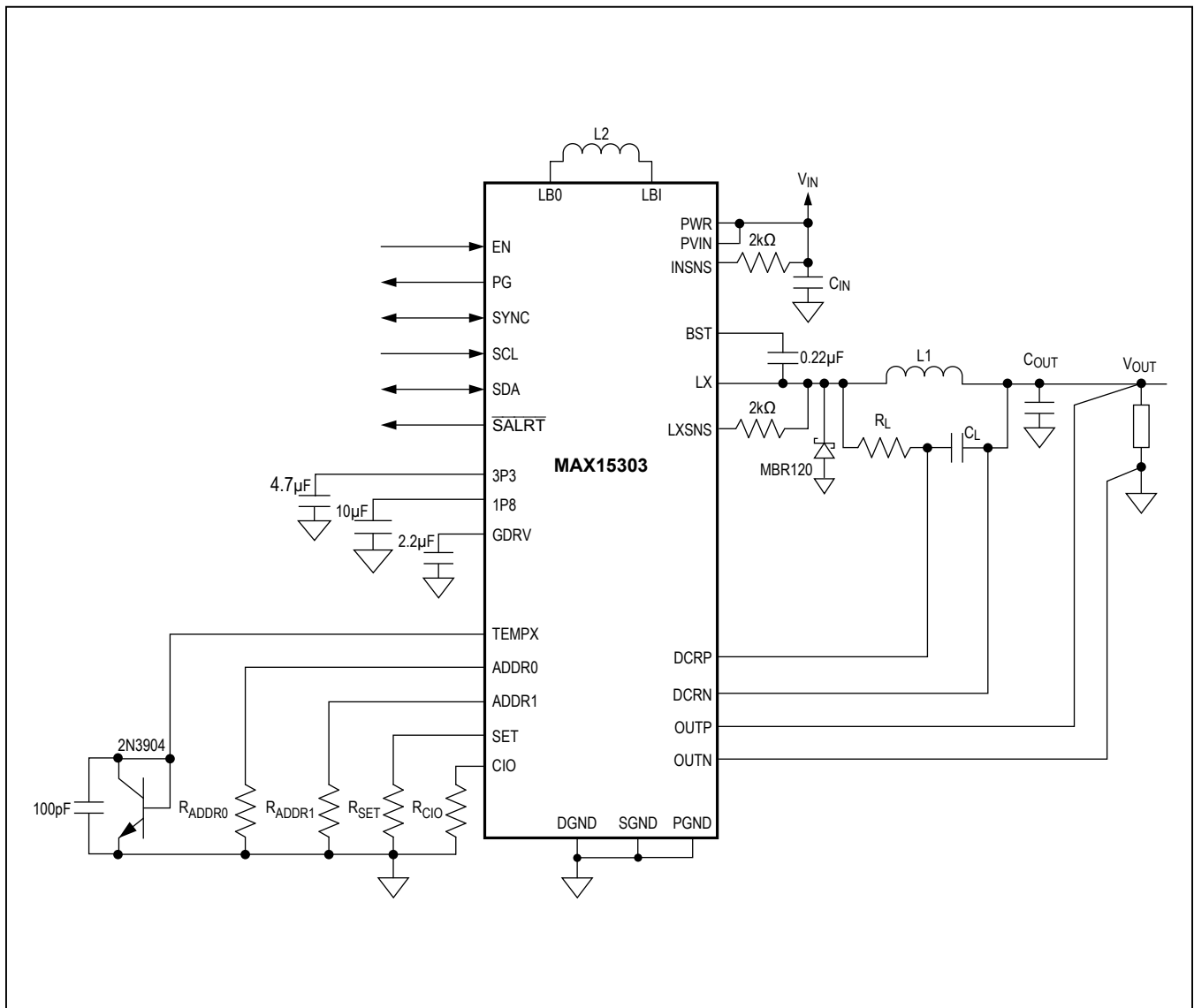
Table 8. Typical Component Values

COMPONENT	APPLICATION 1
Input Supply	12V
Output Voltage	3.3V
R _{SET}	51.1k Ω
Output Current	6A
R _{ADDR1}	5.1k Ω for PMBus 0x30 and IOUT_CAL_GAIN = 4m Ω
R _{ADDR0}	44.2k Ω for PMBus address 0x30
Switching Frequency	600kHz
R _{SYNC}	12.7k Ω
Inductor L1	1.8 μ H, 4m Ω , Würth 7447798180
Inductor L2	10 μ H, Würth 74479889310, 10 μ H, TDK NLCV25T-100K
R _L	2k Ω
C _L	0.22 μ F
Output Capacitance	2 x 100 μ F, X5R, 1206, 6.3V
Input Capacitance	3 x 47 μ F, X5R, 1210, 16V

Thermal Layout

The MAX15303 is available in a small 40-pin, 6mm x 6mm TQFN package with exposed pad to remove heat from the internal semiconductor junctions. The exposed pad must be soldered to the copper on the PCB directly underneath the device package, reducing the θ_{JA} down to approximately 40°C/W. The device shuts down if its temperature increases beyond +115°C (this threshold can be changed using a PMBus command). An evaluation kit is available that demonstrates the recommended layout practices for the device.

Typical Operating Circuit



Ordering Information

PART	TEMP RANGE	PIN-PACKAGE	FIRMWARE
MAX15303AA00+CM	-40°C to +85°C	40 TQFN-EP*	4196
MAX15303AA00+TCM	-40°C to +85°C	40 TQFN-EP*	4196

+Denotes lead(Pb)-free/RoHS-compliant package.

*EP = Exposed pad.

T = Tape and reel.

Package Information

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
40 TQFN-EP	T4066M-5	21-0141	90-0055

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	3/14	Initial release	—
1	1/15	Updated <i>Benefits and Features</i> section	1
2	9/15	Updated <i>Absolute Maximum Ratings</i> and LX row in <i>Pin Description</i> table; added <i>Schottky Diode</i> section, reference design to <i>Typical Operating Circuit</i> , and tape-and-reel package to <i>Ordering Information</i> table	2, 10, 28–31

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim Integrated's website at www.maximintegrated.com.

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